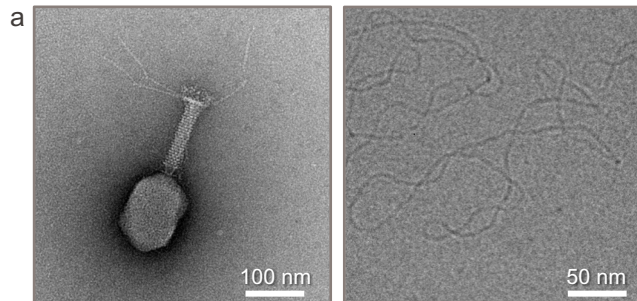




# Transmission Electron Microscopy (TEM)

CCMX Summer School 2023

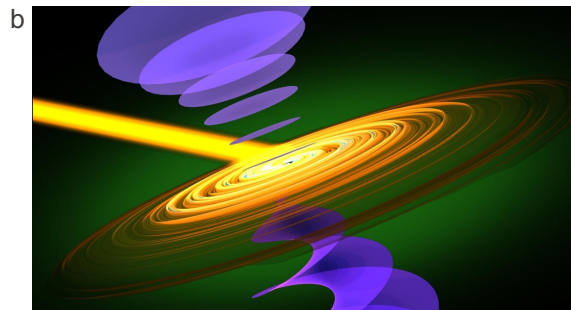
## Biology and life science

T4 virus <sup>a</sup>

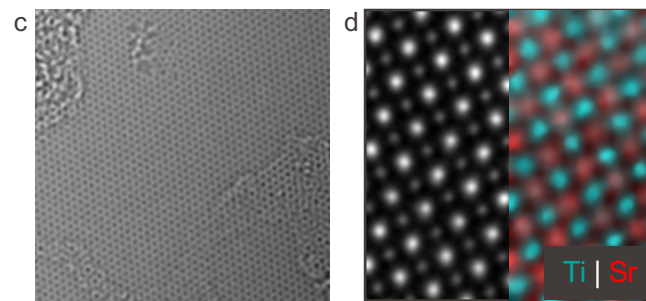
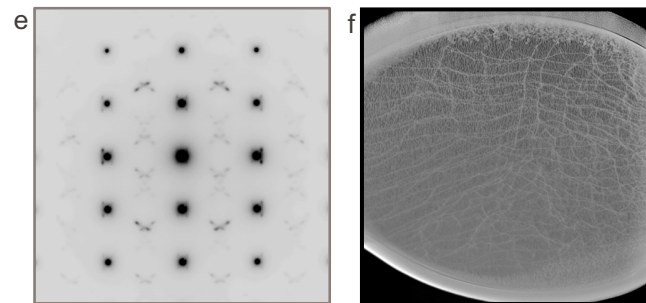
A bacteriophage that infects Escherichia coli bacteria

DNA molecule <sup>a</sup>

## Fundamental physics

Ultrafast electron vortex beams <sup>b</sup>

## Chemistry &amp; materials research

Imaging and spectroscopy at atomic resolution <sup>c,d</sup>Crystallographic studies <sup>e</sup>Analyzing crystal defects <sup>f</sup><sup>a</sup> Images courtesy of Dr. D. Demurtas, CIME-EPFL.<sup>b</sup> Vanacore et al., Nature Materials (2019).<sup>c</sup> Huang et al., Nat. Comm. 2018.<sup>d</sup> Oveisi et al., Ultramicroscopy (2017).<sup>e</sup> Oveisi et al., Scripta Mat. (2013).<sup>f</sup> Bencan et al., Nat. Comm. (2021).

Introduction to transmission electron microscopy (TEM)

TEM imaging and diffraction

High-resolution TEM

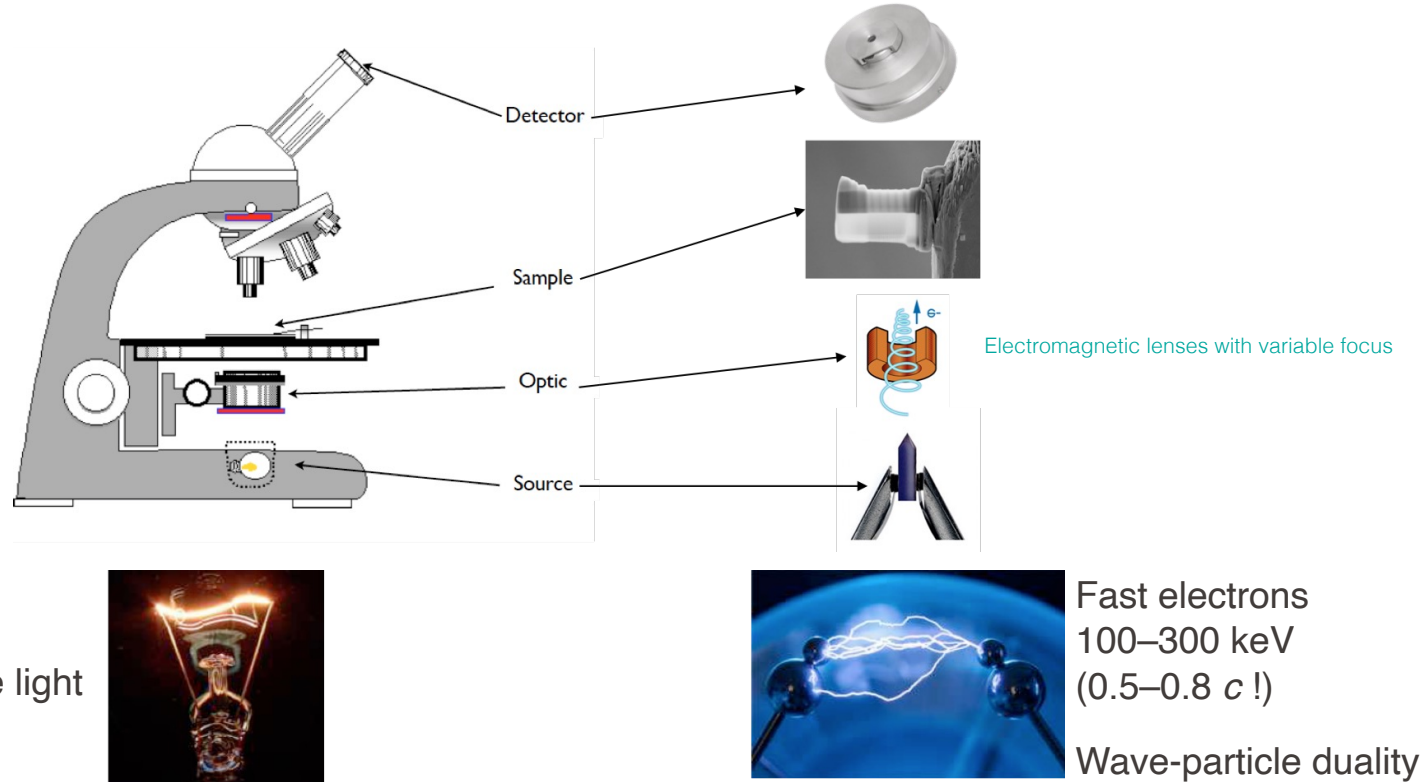
Scanning TEM (STEM)

Energy-dispersive X-ray (EDX) analysis in STEM

Electron energy-loss spectroscopy (EELS)

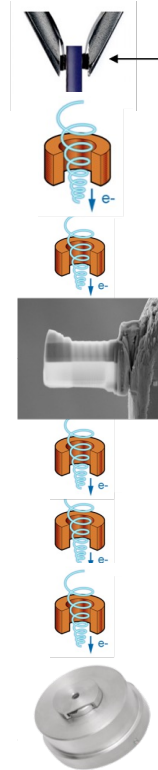
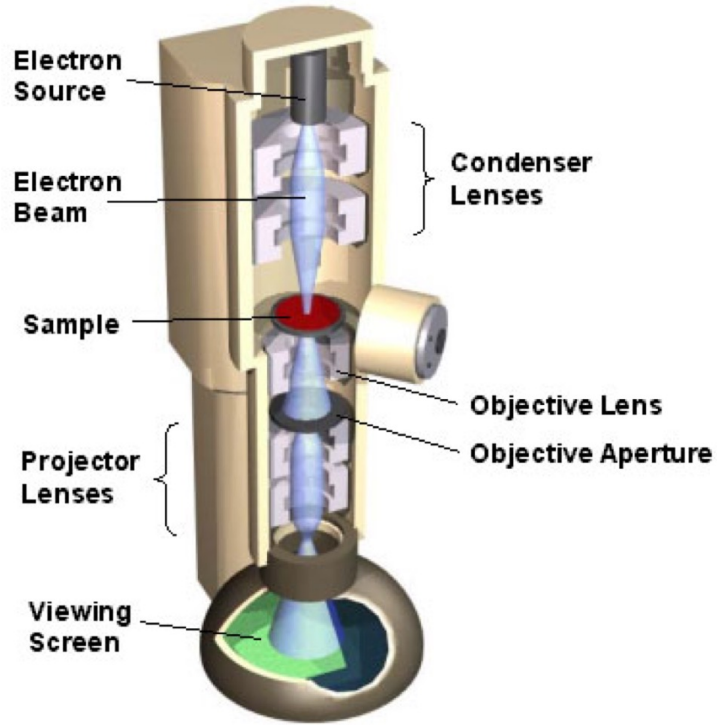
*In situ* TEM

Summary

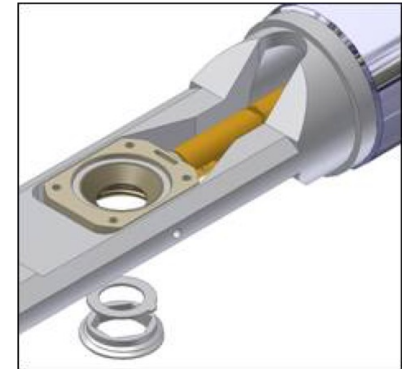
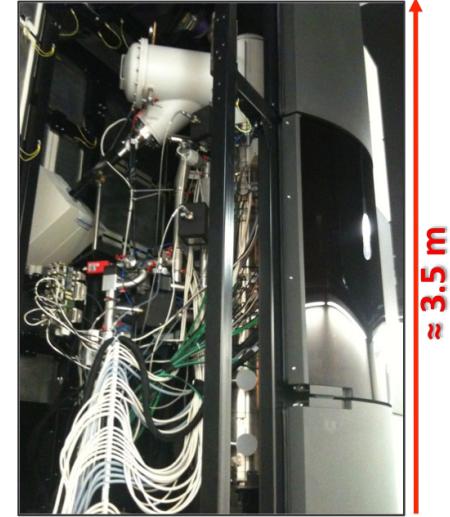


Can consider analogous to projection light microscopy, but with better resolution





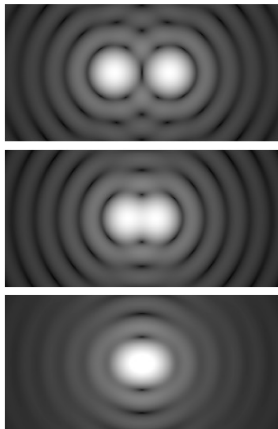
Double Cs-corrected FEI Titan-Themis @ CIME-EPFL



Specimen should be electron transparent:  
several nanometers thick

The resolution of an optical microscope is defined as the minimum distance between two point sources (e.g. objects) such that their presence can be distinguished in the image.

Abbe's definition of maximum resolution of an optical system states that the smallest feature resolved is limited by diffraction.



Airy Diffraction Disks

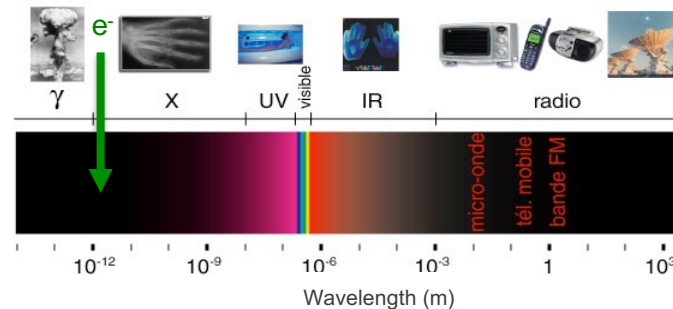
Visible light:  $\lambda \approx 300\text{-}700\text{ nm}$   $\rightarrow$  resolution around half of the  $\lambda$

Electrons:  $\lambda = h \cdot c / E$  : Wave-particle duality

@ 200 keV:  $\lambda = 0.025\text{ \AA}$  << interatomic spacing\*

$$r = \frac{1.22\lambda}{2\sin\theta} \approx \frac{0.61\lambda}{\theta}$$

For the 200 keV TEM around  $< 1\text{ \AA}$  resolution possible



\*Aberrations & instabilities  $\rightarrow$  Actual resolution around  $25\text{-}50\lambda$ , but atomic/sub- $\text{\AA}$  resolution possible in TEM

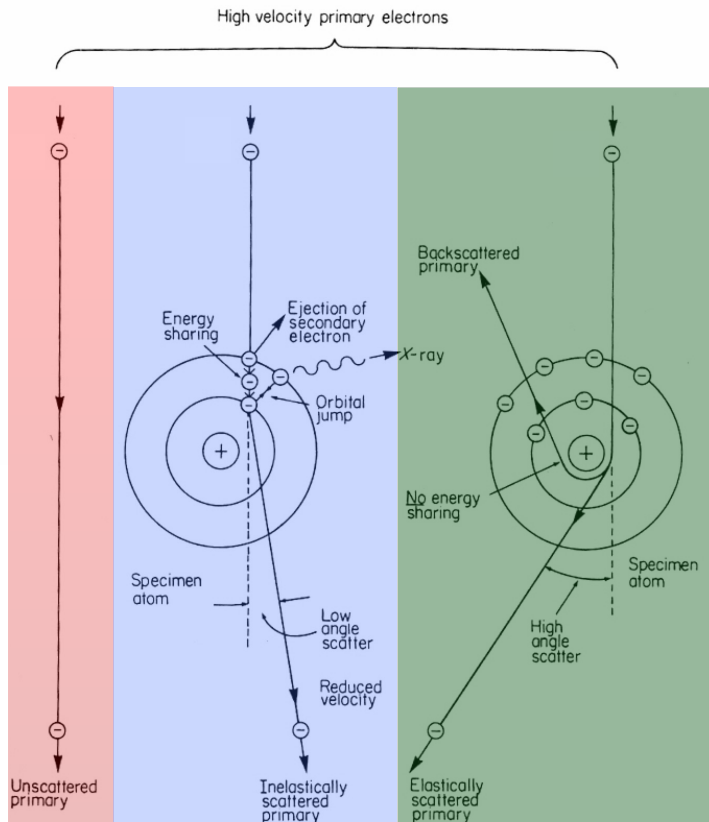
# Why fast electrons?

	Advantageous	Disadvantageous
Visible light	Not very damaging Easily focused Eye detector	Long wavelengths (400 nm)
X-rays	Small wavelength (Angstrom) Good penetration	Hard to focus Damage sample
Neutrons	Low sample damage Small wavelength (pm)	How to produce? How to focus?
<b>Electrons</b>	<b>Small wavelength (pm)</b> <b>Can be focused to a sub-Å size probe</b> <b>Wave-particle duality</b>	<b>Damage sample</b> <b>Poor penetration (&lt; x00 nm)</b>

High energy electrons have a short wavelength  
 Easy to produce high brightness electron beams  
 Easy to manipulate: focused  
**Interact strongly with matter**

Electron microscopes are used not only for obtaining good resolution images but also:

- **can be used as a diffractometer (TEM and EBSD)**
- **for chemical analyses (SEM and TEM)**
- **for imaging/measuring strain field in the sample (SEM and TEM)**
- **etc.**



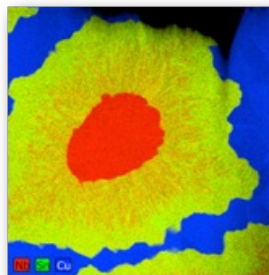
**Inelastic events:** The result is a **transfer of beam energy** to the specimen atom (**energy loss**) and a potential expulsion of an electron from that atom as a **secondary electron (SE)**.

If the vacancy due to the creation of a secondary electron is filled from a higher level orbital, an X-Ray or Auger characteristic of that energy transition is produced.



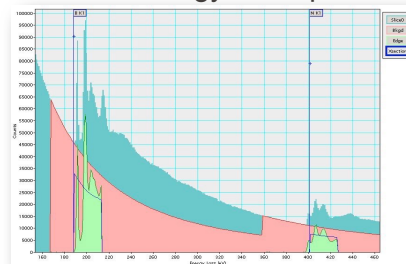
That's why TEMs are shielded!

Characteristic X-rays

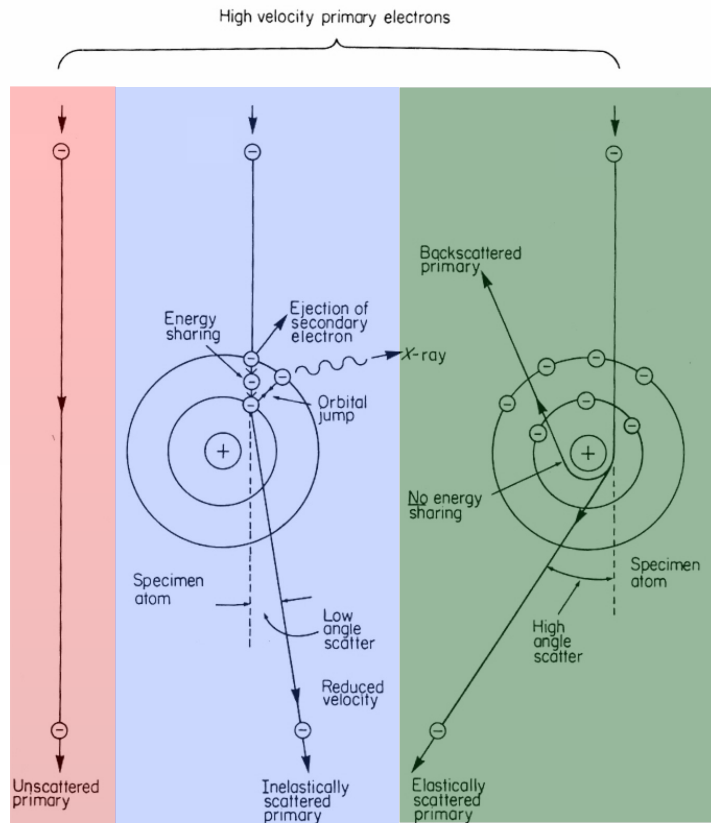


Chemical composition

Electron energy-loss spectrum



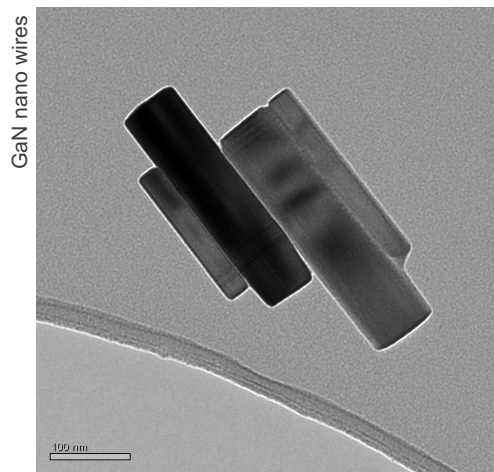
Chemical composition, band-gap & optical properties



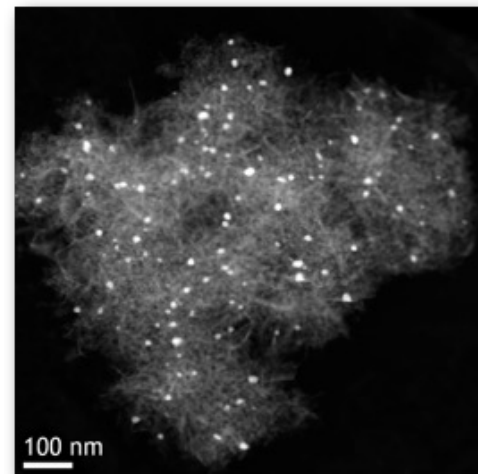
**Elastic events** occur when a beam electron interacts with the electric field of the nucleus or electron cloud of a specimen atom (Coulomb forces), resulting in a change in the direction of the beam electron **without a significant change in the energy** of the beam electron ( $< 1$  eV).

Coulombic interaction within the electron cloud, Low-angle scattering  
Coulombic attraction by the nucleus, Higher-angle scattering

Thicker specimen or larger nucleus  $\rightarrow$  More scattering



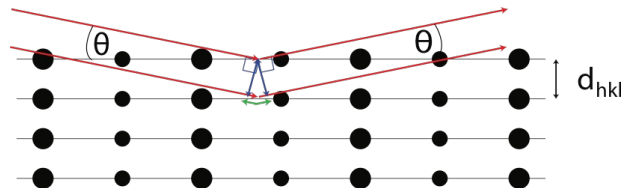
Mass/thickness contrast  
Bright-field TEM image



Mass/thickness contrast  
HAADF-STEM image

# $e^-$ as wave & Bragg scattering

For X-ray diffractometer



## X-ray scattering:

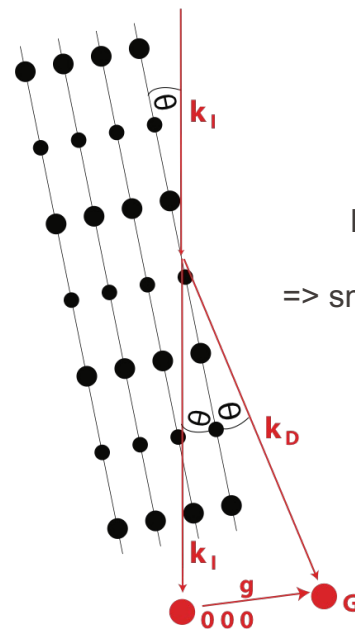
Path difference between reflection  
from planes distance  $d_{hkl}$  apart  
 $= 2d_{hkl} \sin\theta$

$\Rightarrow$  Bragg law:  
 $n\lambda = 2d_{hkl} \sin\theta$

or

$$\lambda = 2d_{nhnknl} \sin\theta$$

For TEM electrons come from top, but  
otherwise geometrically the same

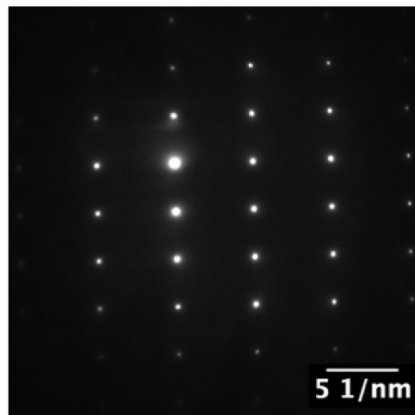


Electron diffraction:  $\lambda \sim 0.001 \text{ nm}$   
therefore:  $\lambda \ll d_{hkl}$   
 $\Rightarrow$  small angle approximation:  $\lambda \approx 2d_{nhnknl} \theta$

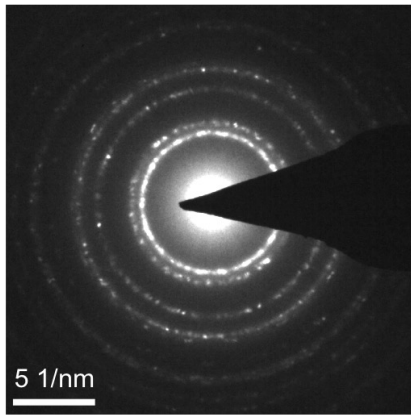
$\Rightarrow$  Bragg diffraction at angle  $2\theta$

# $e^-$ as wave & Bragg scattering

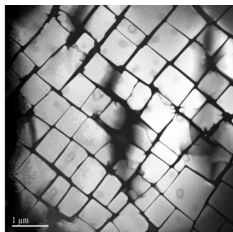
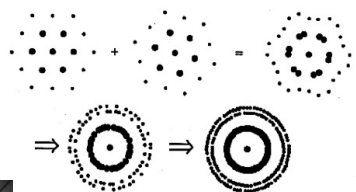
Electron diffraction pattern



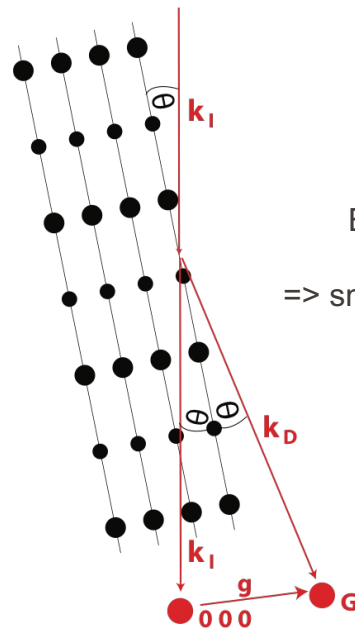
Spot pattern from a single crystal  
Spots represent different (hkl) planes



Ring pattern as many crystallites oriented differently in diffraction conditions



Therefore TEM gives image & diffraction!



Electron diffraction:  $\lambda \sim 0.001 \text{ nm}$   
therefore:  $\lambda \ll d_{hkl}$

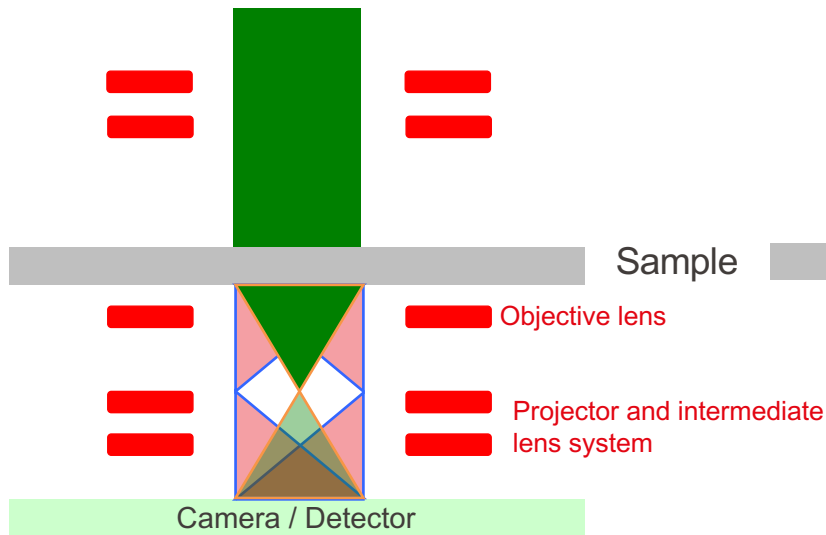
$\Rightarrow$  small angle approximation:  $\lambda \approx 2d_{hkl}\sin\theta$

$\Rightarrow$  Bragg diffraction at angle  $2\theta$



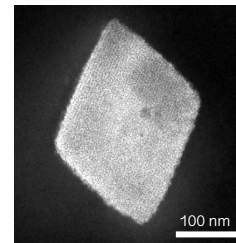
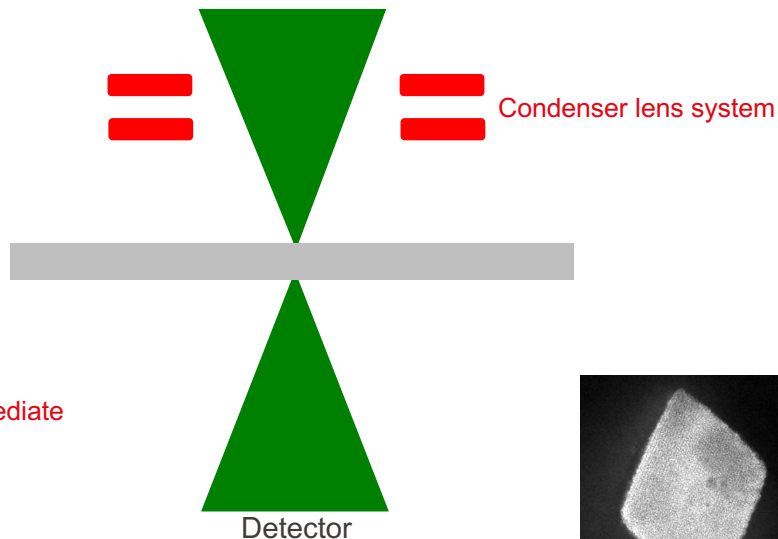
## Conventional TEM

Electron beam (60-300 keV)



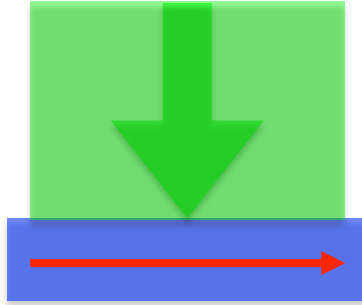
## Scanning mode (STEM)

Electron beam (30-300 keV)



2D projection of a 3D object

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



Sample (thin,  
 $e^-$  transparent)

← Objective lens →



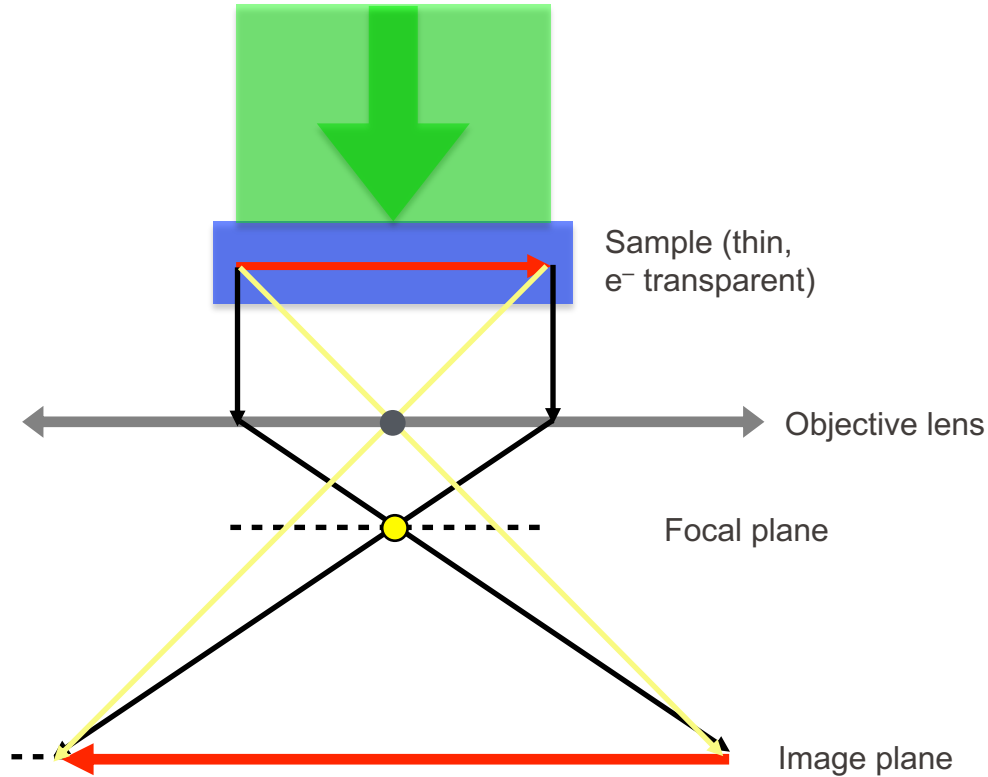
Focal plane



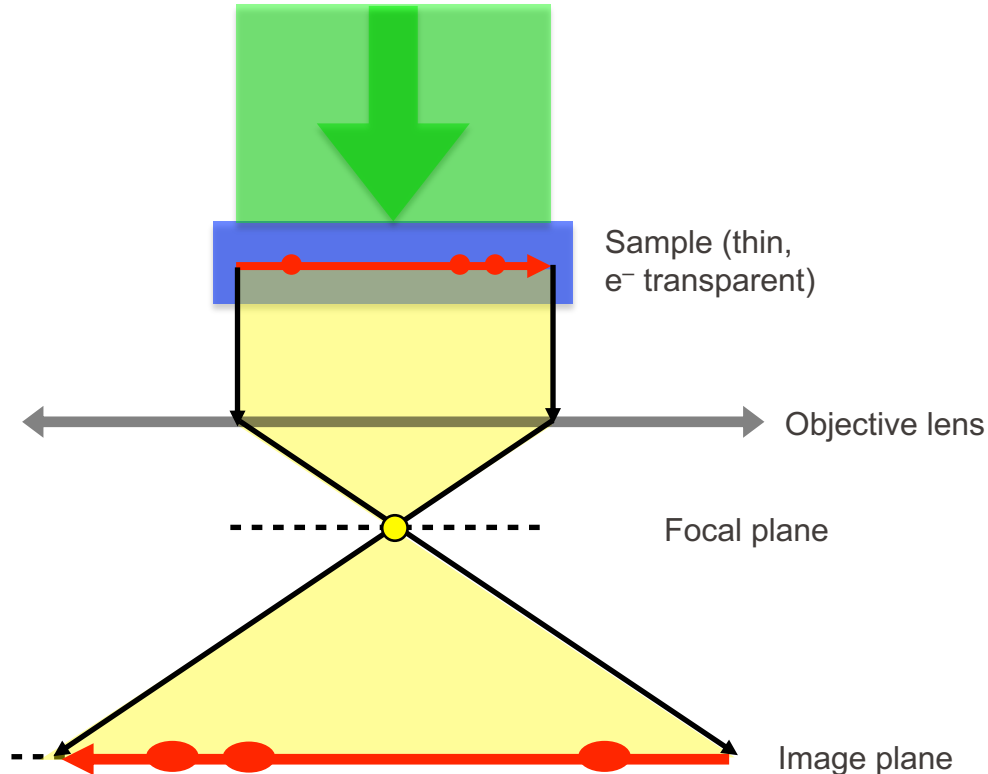
Image plane



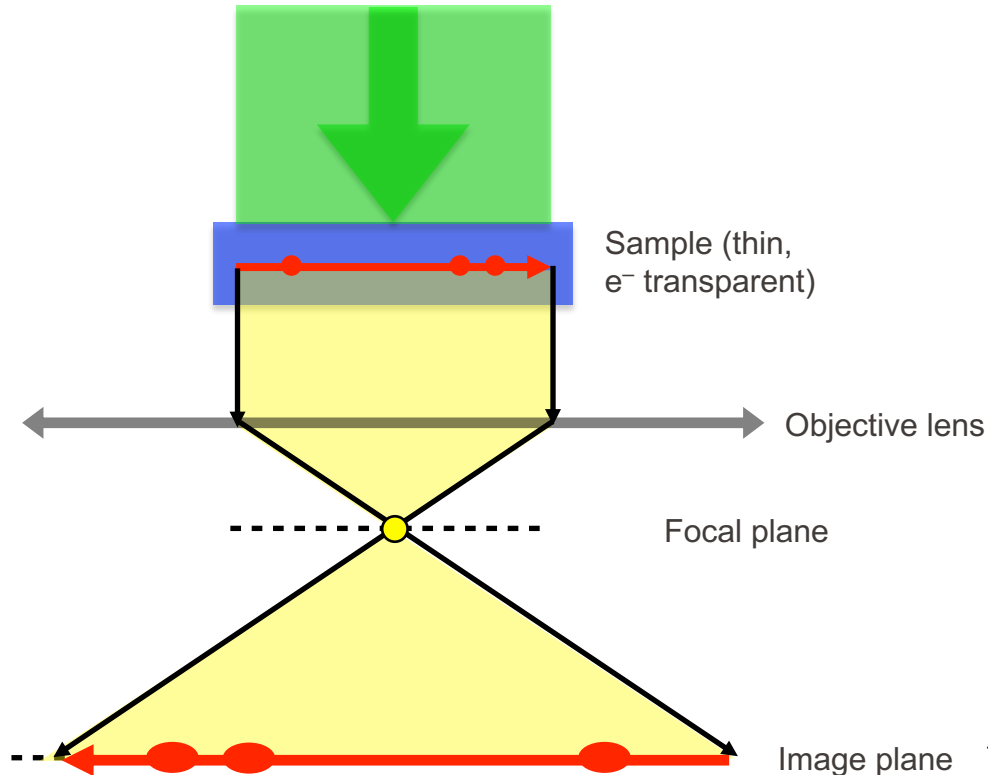
Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

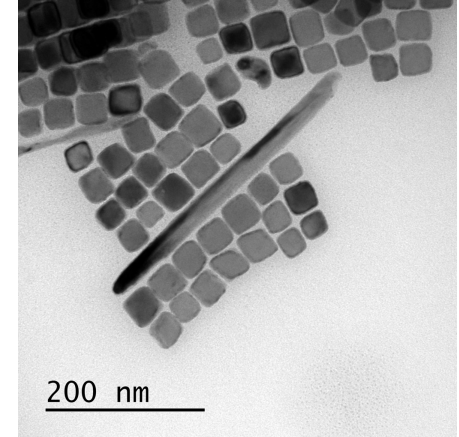


Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



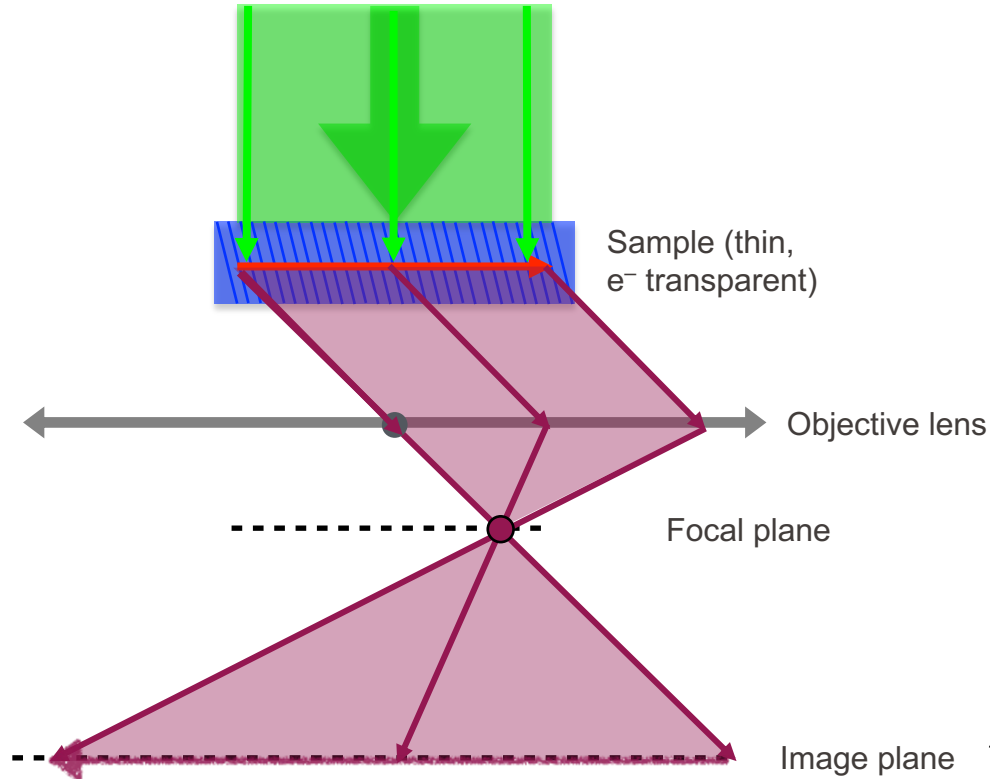
**Why some cubic particles appear darker than others?**

Cubic particles ( $\approx 40 \text{ nm}$ ) of Cu

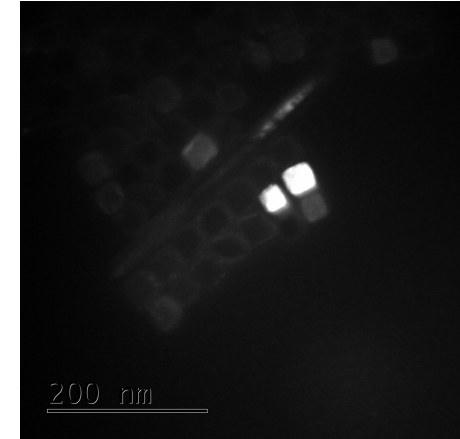
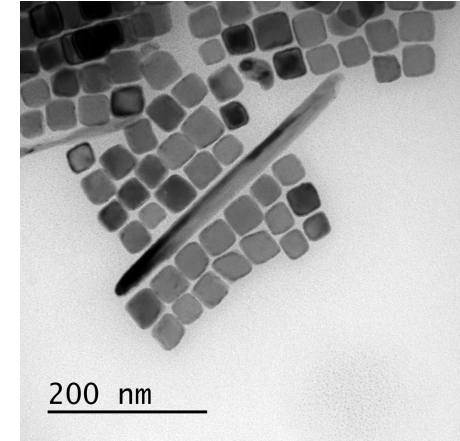


Bright-field image:  
made by directly transmitted electrons

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

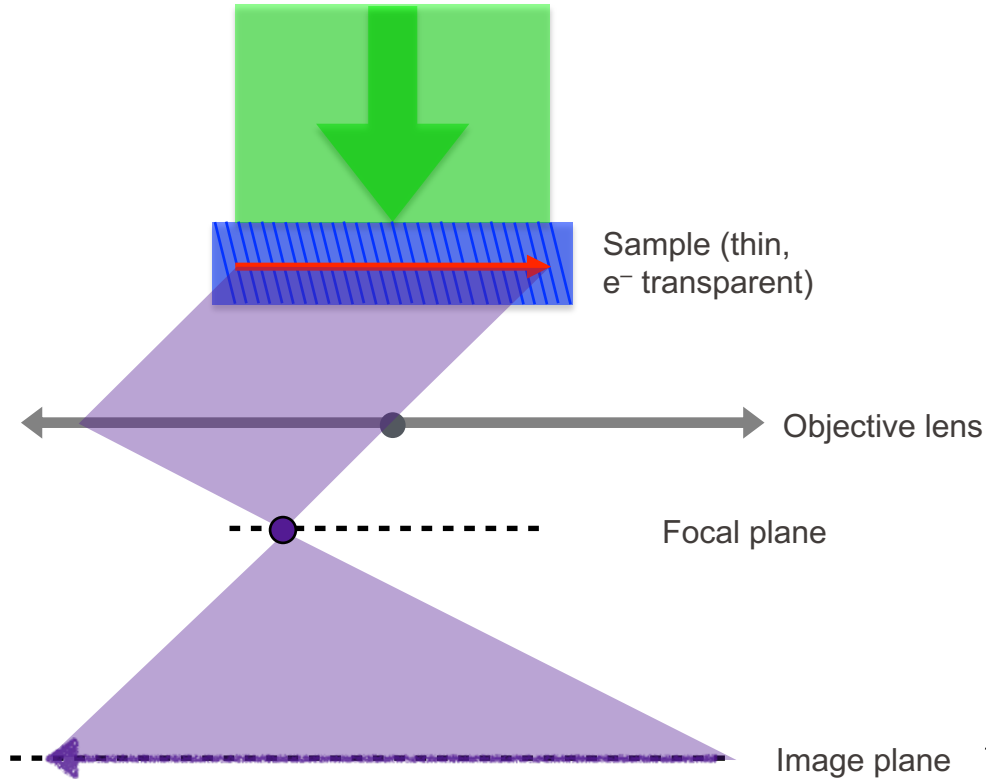


Bright-field image

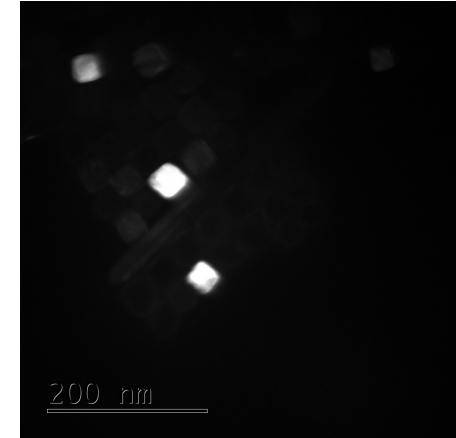
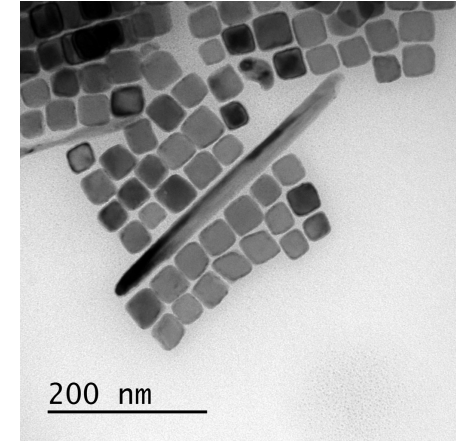


Dark-field image:  
made by selected diffracted electrons

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$



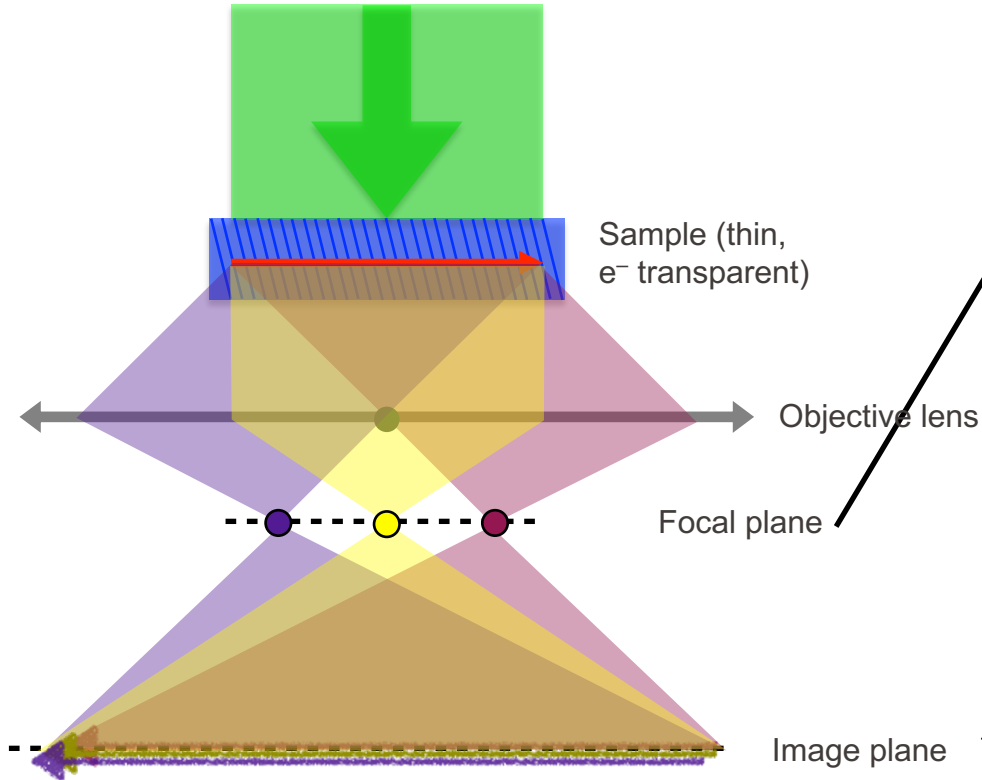
Bright-field image



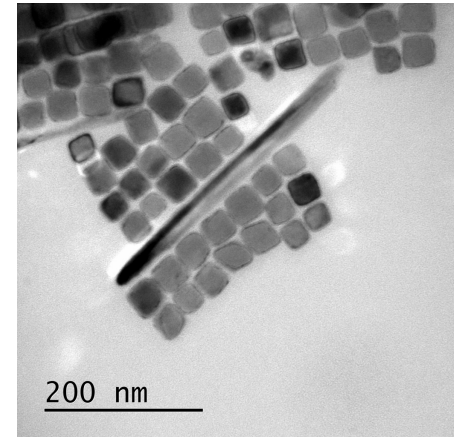
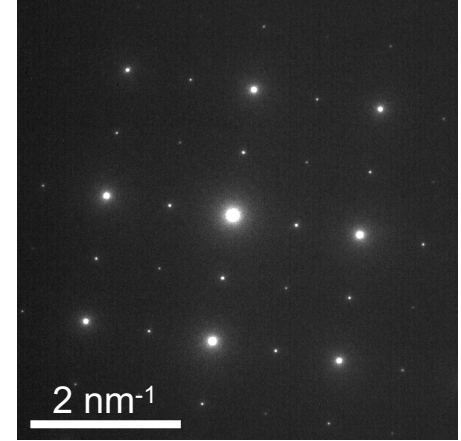
Dark-field image:  
made by selected diffracted electrons



Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

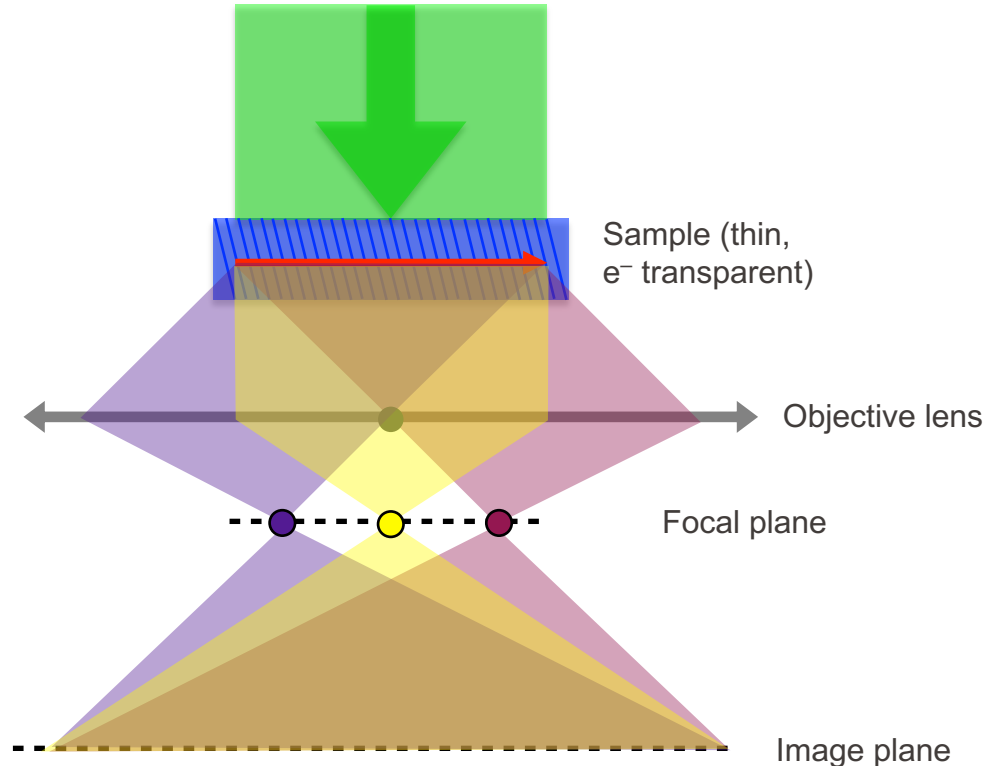


Electron diffraction pattern

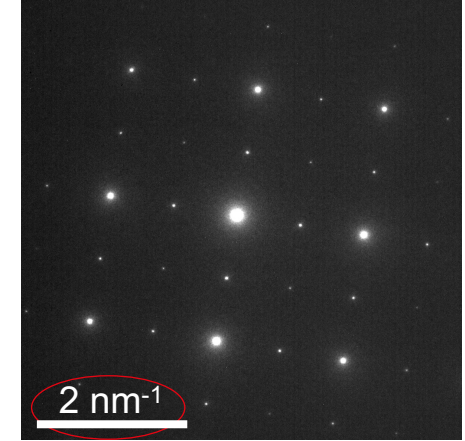


Ghost image:  
Superposition of images made  
by direct and diffracted electrons

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

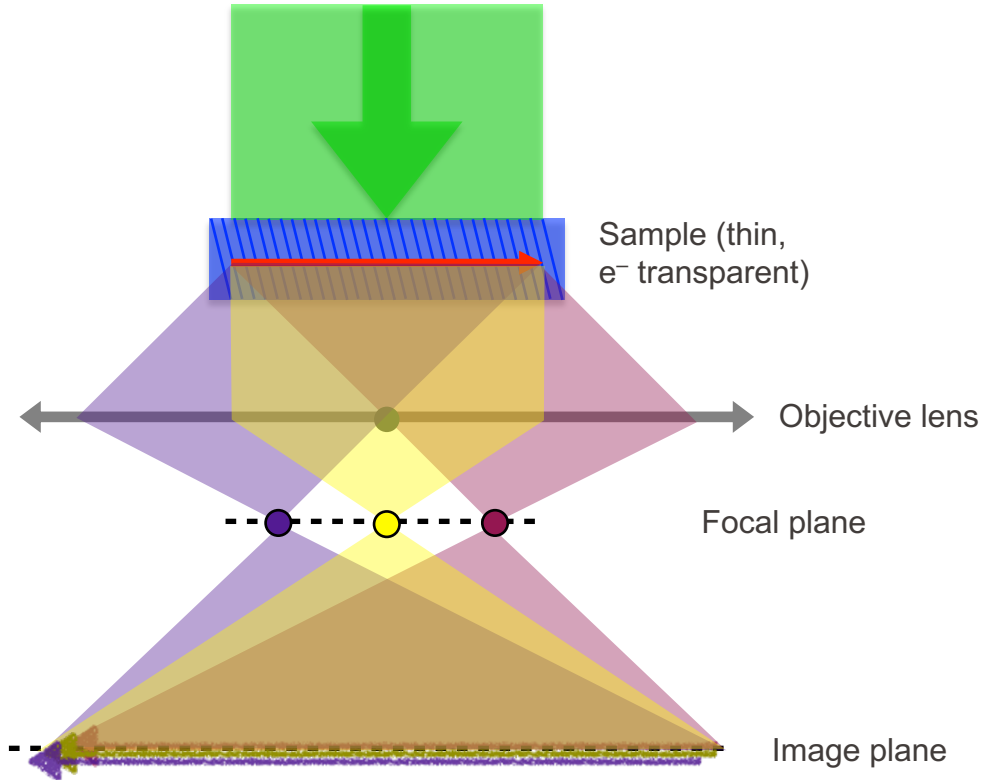


Electron diffraction pattern

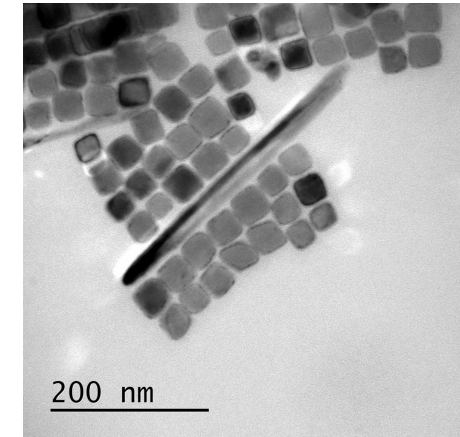
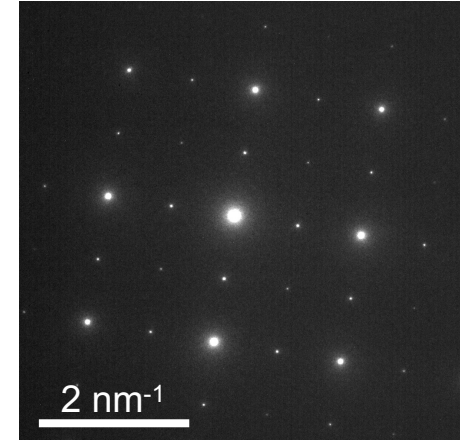


- *In back focal plane of objective lens parallel rays focused to point*
- *Diffraction – coherent scattering – creates sets of parallel rays from different crystal planes*
- *Focusing of these parallel rays in back focal plane creates spots of strong intensity:  
**the diffraction pattern***

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

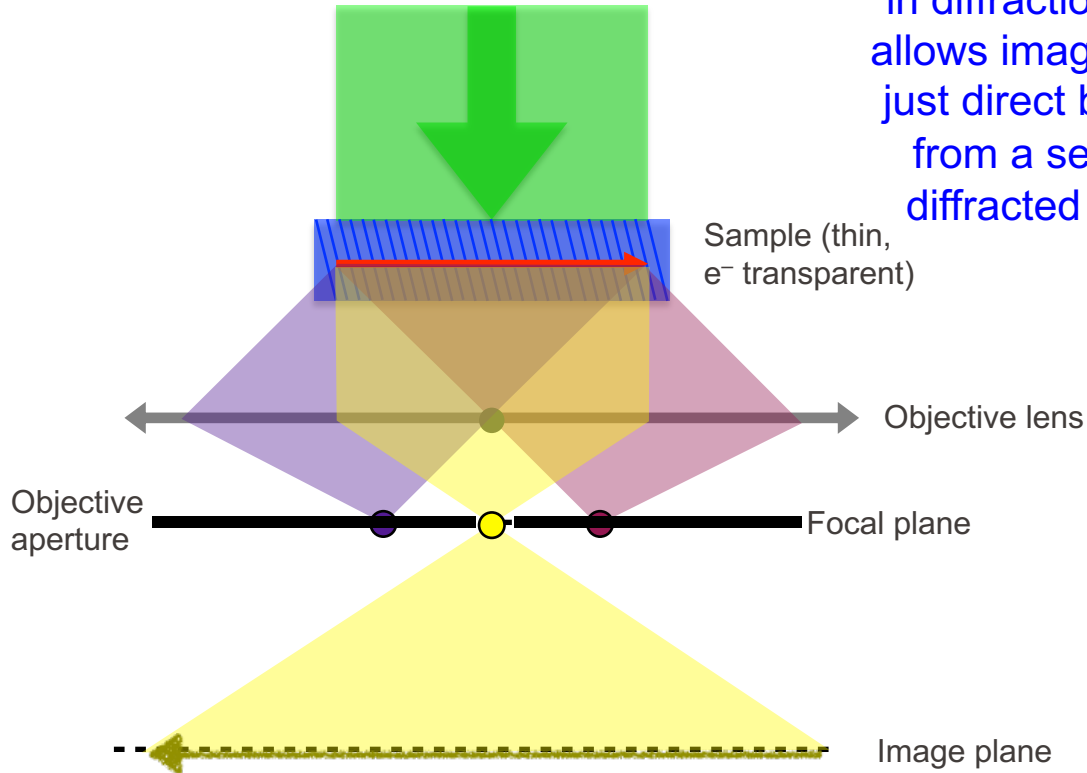


Electron diffraction pattern

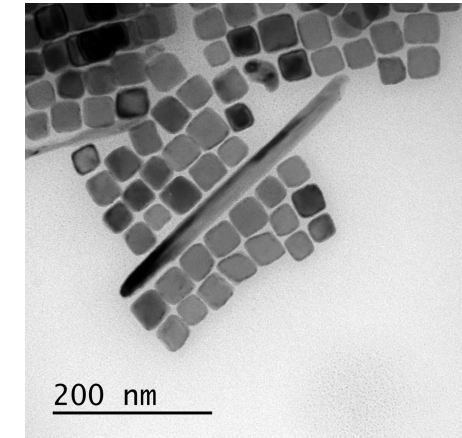
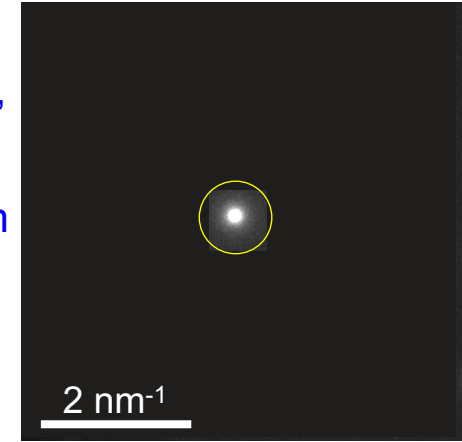


Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

Insertion of the  
“objective aperture”  
in diffraction plane  
allows imaging from  
just direct beam or  
from a selected  
diffracted beam.



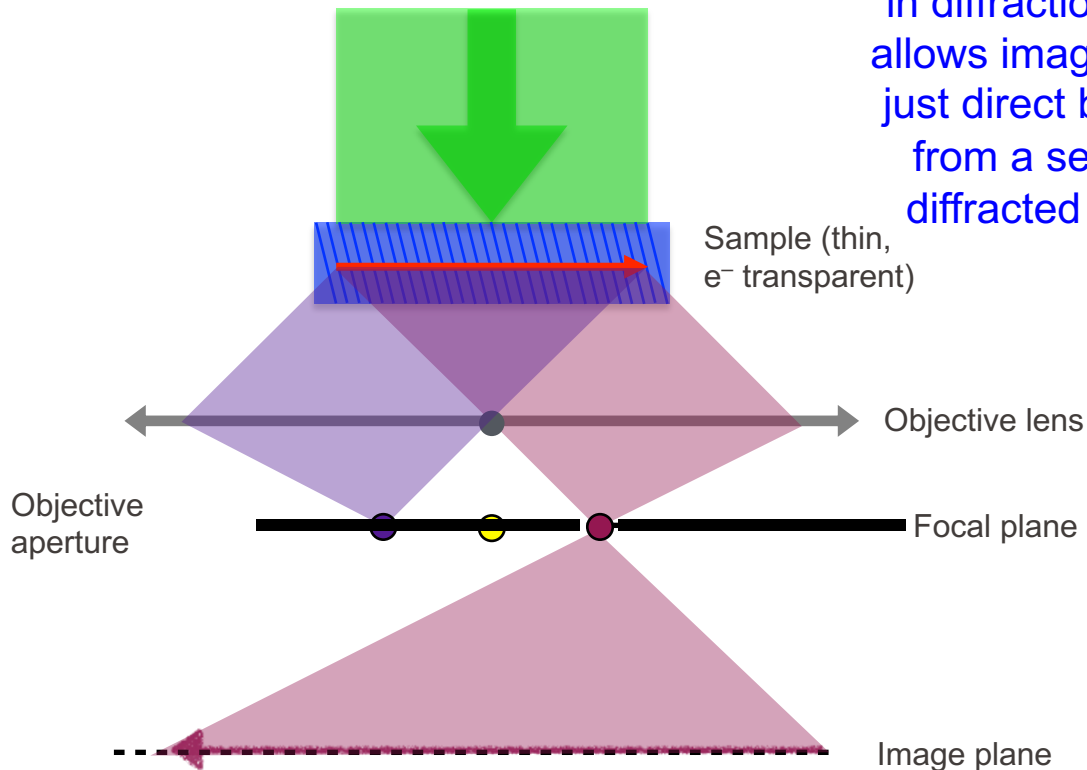
Electron diffraction pattern



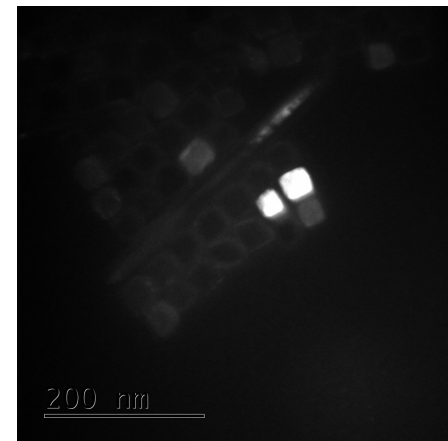
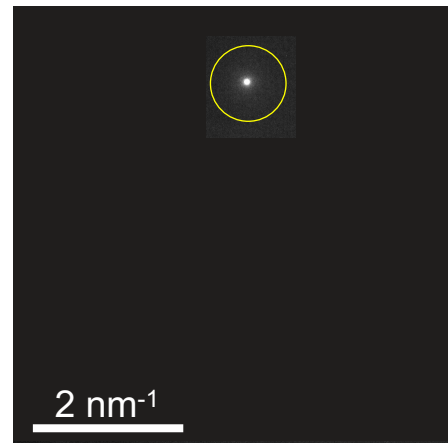
Bright-field image:  
made by directly transmitted electrons

Parallel incident  $e^-$  beam;  $\lambda \approx 0.02\text{--}0.03 \text{ \AA}$

Insertion of the  
“objective aperture”  
in diffraction plane  
allows imaging from  
just direct beam or  
from a selected  
diffracted beam.



Electron diffraction pattern



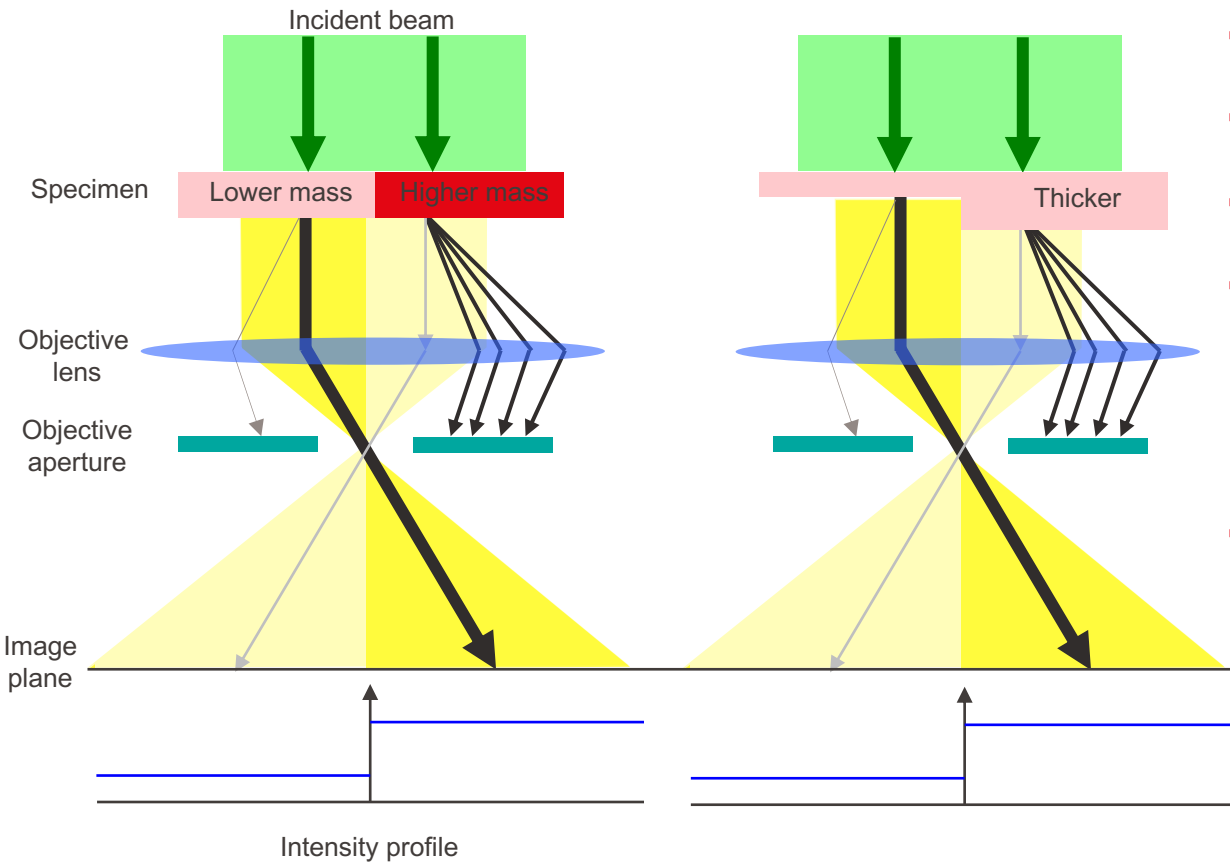
Dark-field image:  
made by selected diffracted electrons

## ■ Image formation in TEM

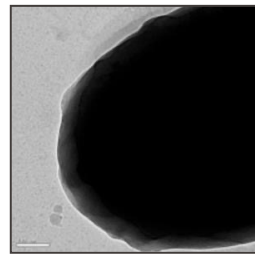
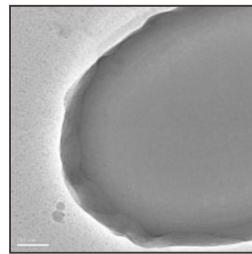
- Image and diffraction modes
- Bright- and dark-field modes
- High-resolution TEM

## ■ Image contrast in TEM

- Mass-thickness contrast
- Diffraction contrast
- Phase contrast

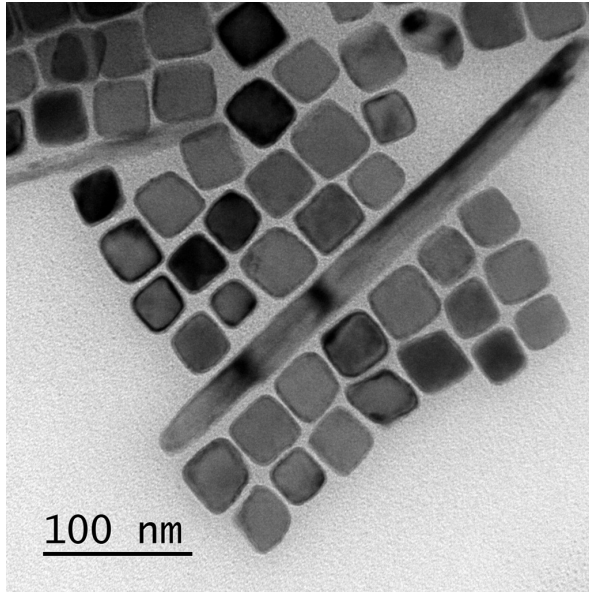


- Areas of higher mass/thickness scatter electrons more than others.
- Electrons are captured by the aperture and lost from the beam path.
- Areas of higher mass thickness will therefore appear dark in the image.
- This is known as:
  - **mass thickness contrast,**
  - **scattering contrast,**
  - **aperture contrast or**
  - **amplitude contrast!**
- Applies to both Crystalline and Amorphous materials.

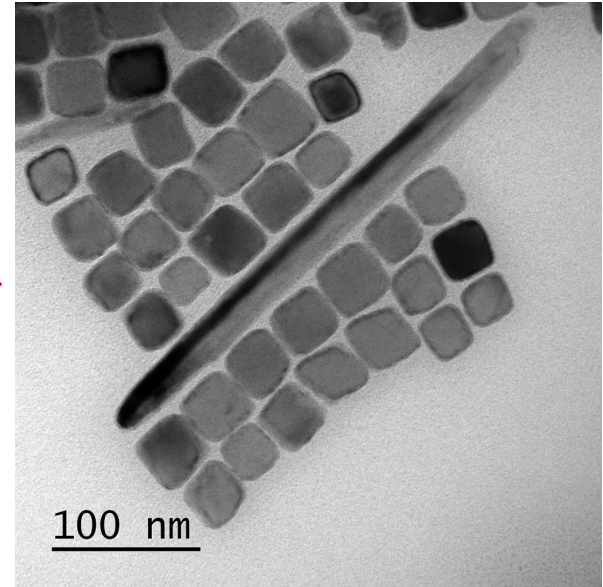




### Example: Copper nano particles

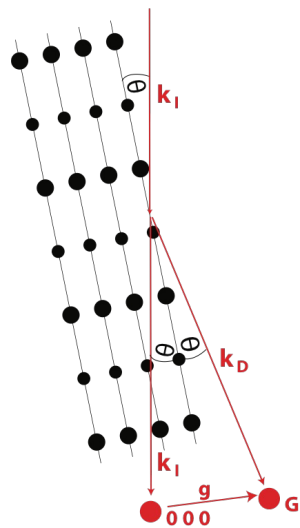


Tilting the sample



**Why some of cubic particles appear darker than others?**

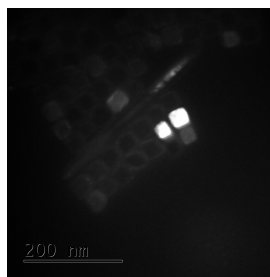
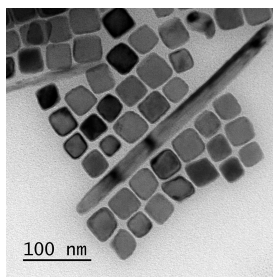
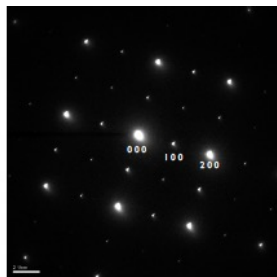
Note that contrast changes when tilting the specimen



Path difference between reflection  
from planes distance  $d_{hkl}$  apart  
 $= 2d_{hkl} \sin\theta$

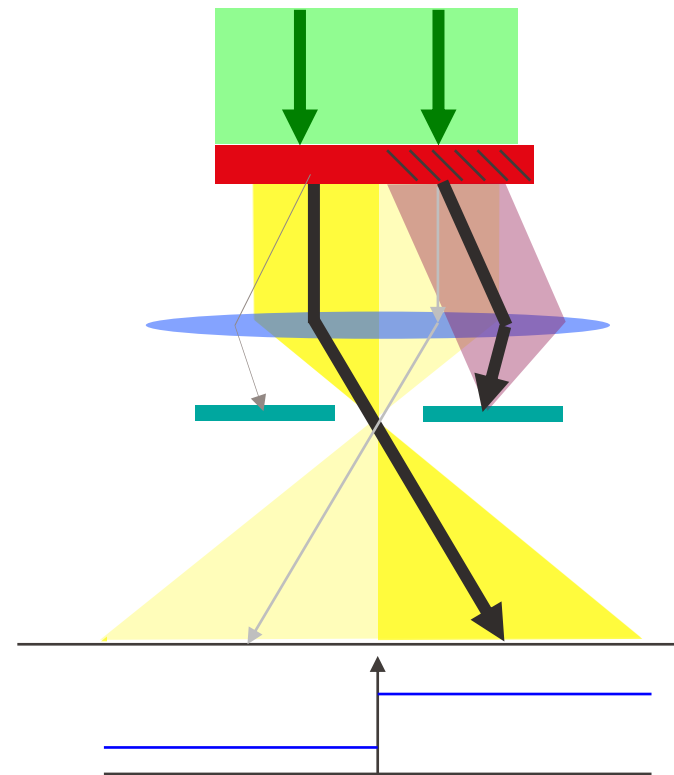
$$\text{Bragg law: } \lambda = 2d_{hkl} \sin\theta$$

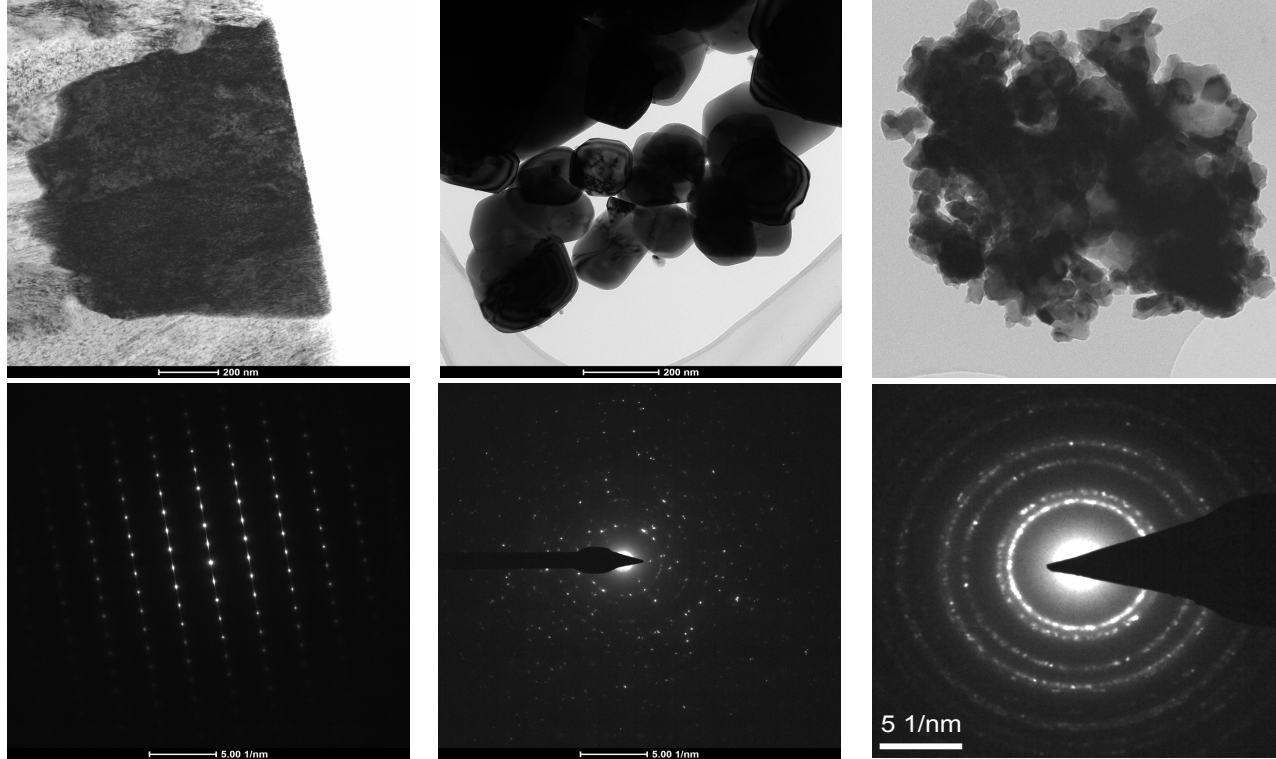
→ Bragg diffraction at angle  $2\theta$



TEM gives image & diffraction information!

### Diffraction contrast





## Principle of diffraction contrast imaging:

Typically we use an objective aperture to select either the direct beam or a specific diffracted beam in the back-focal plane.

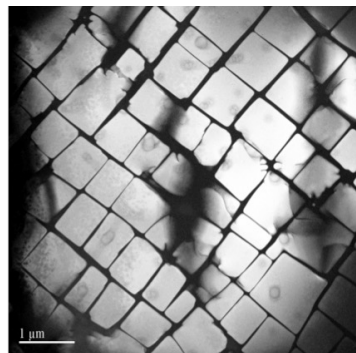
If the diffraction condition changes across the sample the intensity in the selected beam changes; the intensity in the image changes correspondingly.

In other words we make a spatial map of the intensity distribution across the sample in the selected beam: *it is a mapping technique*.

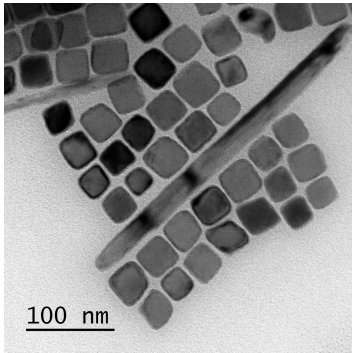
In this way we can image changes in crystal phase and structural defects such as dislocations

As an example such TEM imaging was a key piece of evidence proving the existence of dislocations

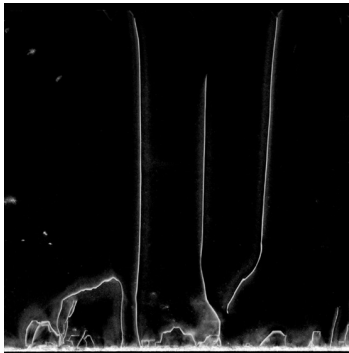
## Examples of diffraction contrast image



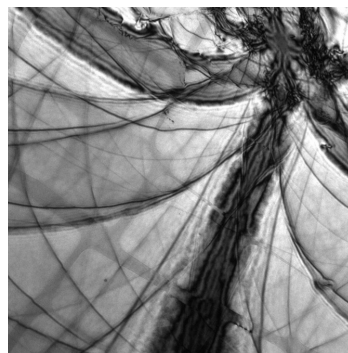
Dark-field (DF) image  
Precipitates in NiAl super-alloy



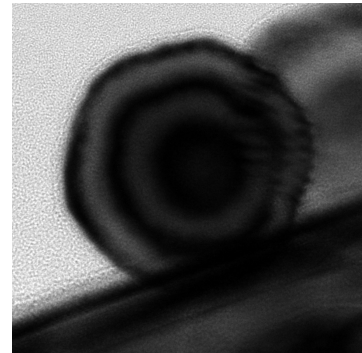
Bright-field (BF) image  
Cu Nanocubes



Weak beam dark-field image  
Dislocations in GaN



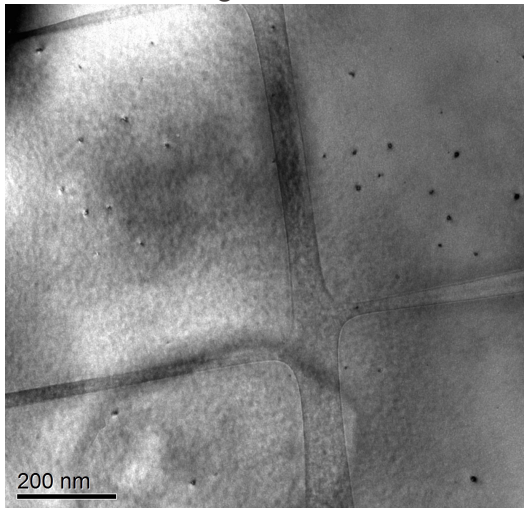
Bright-field image of bent  
regions in NiAl super-alloy  
= Bend contours



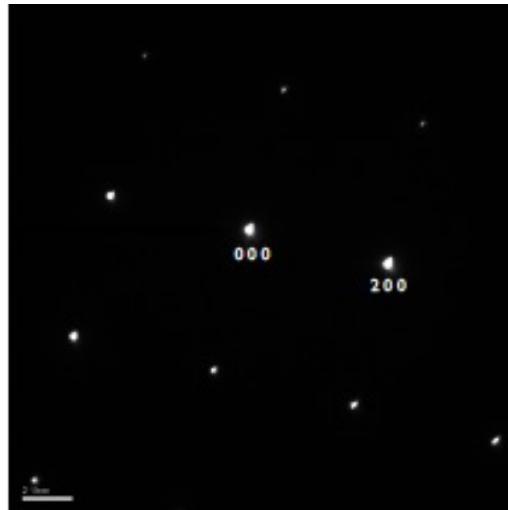
Thickness fringes in BF-TEM  
image of a Cu nanocube

## Example: $\text{Ni}_3\text{Al}$ -based superalloy

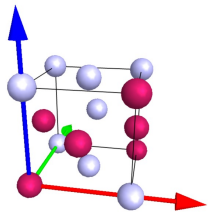
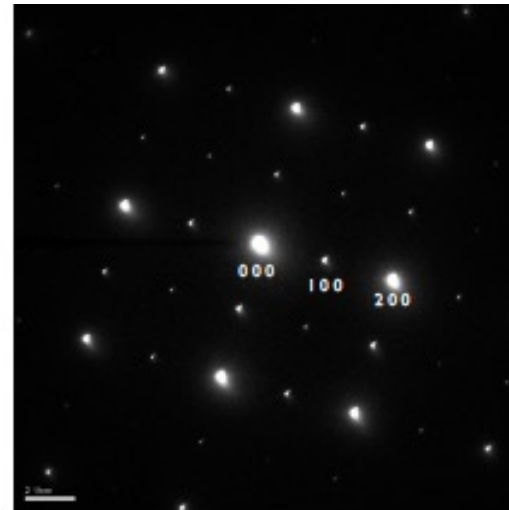
Bright-field



$\gamma$ -phase matrix: FCC  
(Ni, Al disordered on sites)



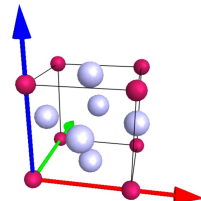
$\gamma'$ -phase precipitate: primitive cubic  
(Ni on face centres, Al on corners)



Which reflection to use to discriminate the the  $\gamma'$ -phase precipitate from the matrix?

- a)  $\{200\}$  of  $\gamma'$ -phase precipitate
- c)  $(000)$  direct beam

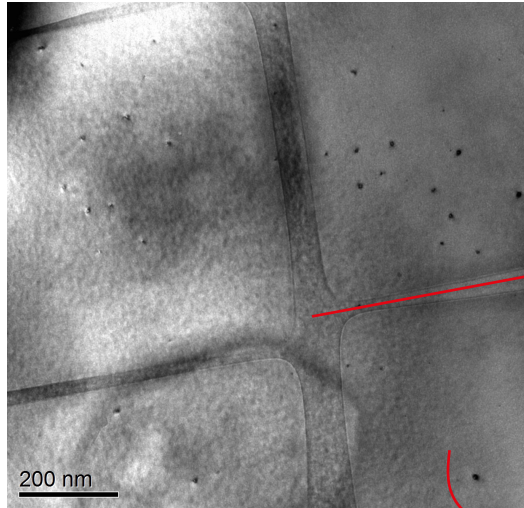
- b)  $\{200\}$  of  $\gamma$ -phase matrix
- d)  $\{100\}$  of  $\gamma'$ -phase precipitate



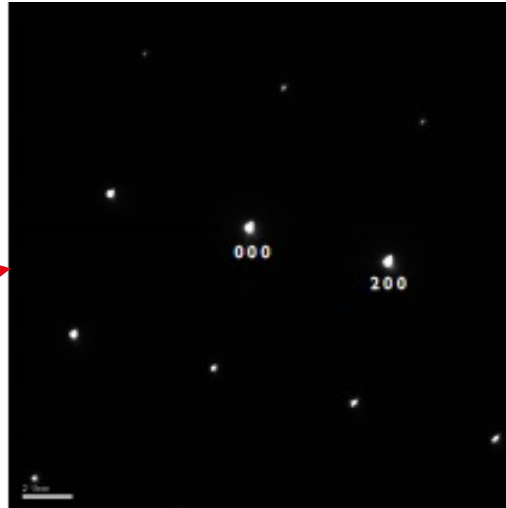


## Example: $\text{Ni}_3\text{Al}$ -based superalloy

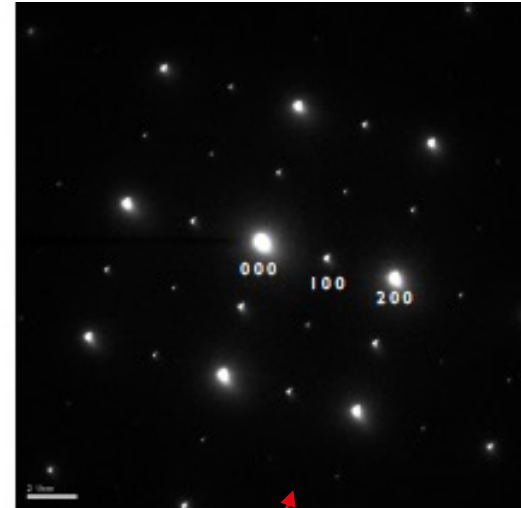
Bright-field



$\gamma$ -phase matrix: FCC  
(Ni, Al disordered on sites)



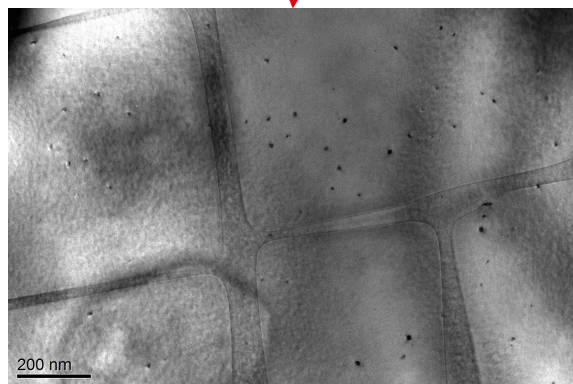
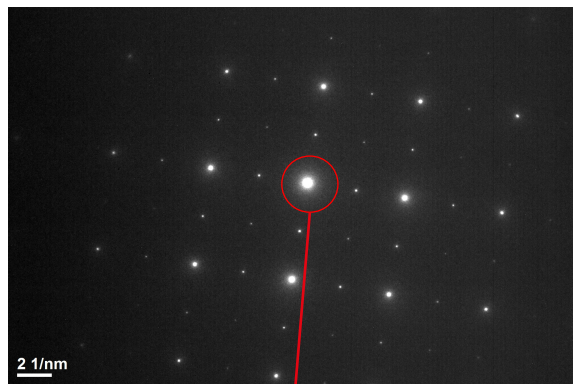
$\gamma'$ -phase precipitate: primitive cubic  
(Ni on face centres, Al on corners)



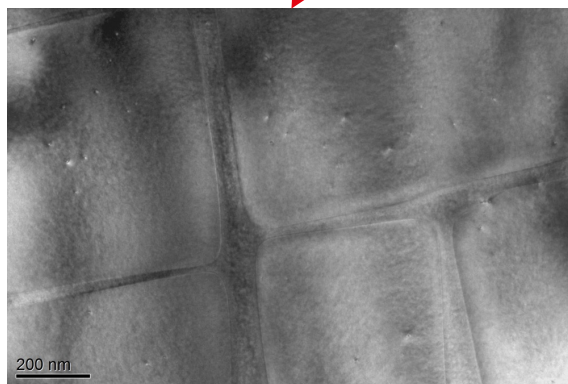
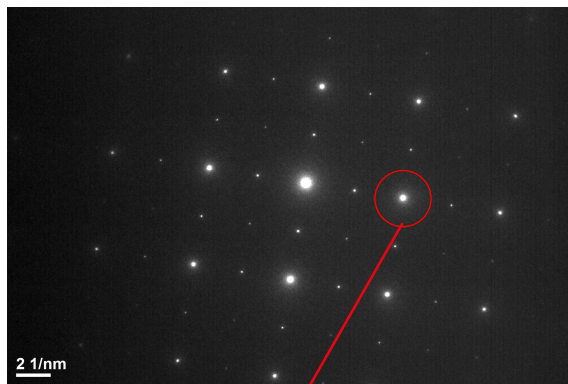
**Note:** EDX can't discriminate these two crystal phases!



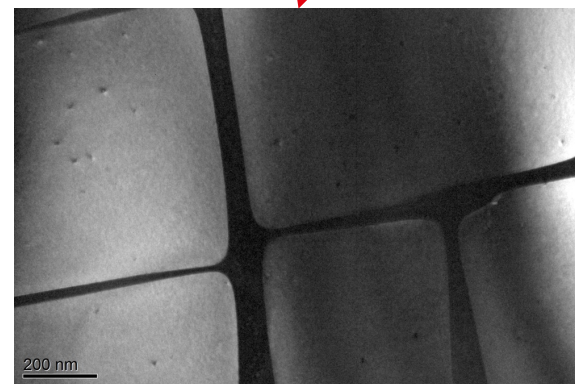
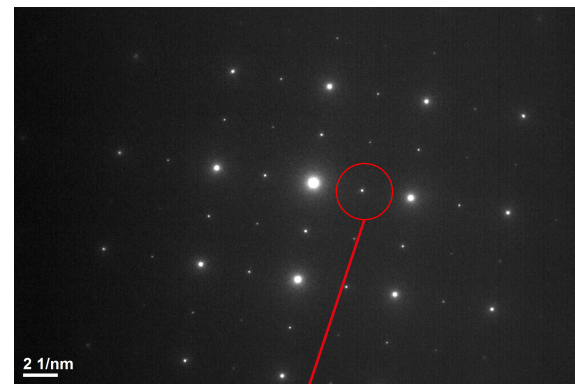
Example:  $\text{Ni}_3\text{Al}$ -based superalloy



Bright-field image

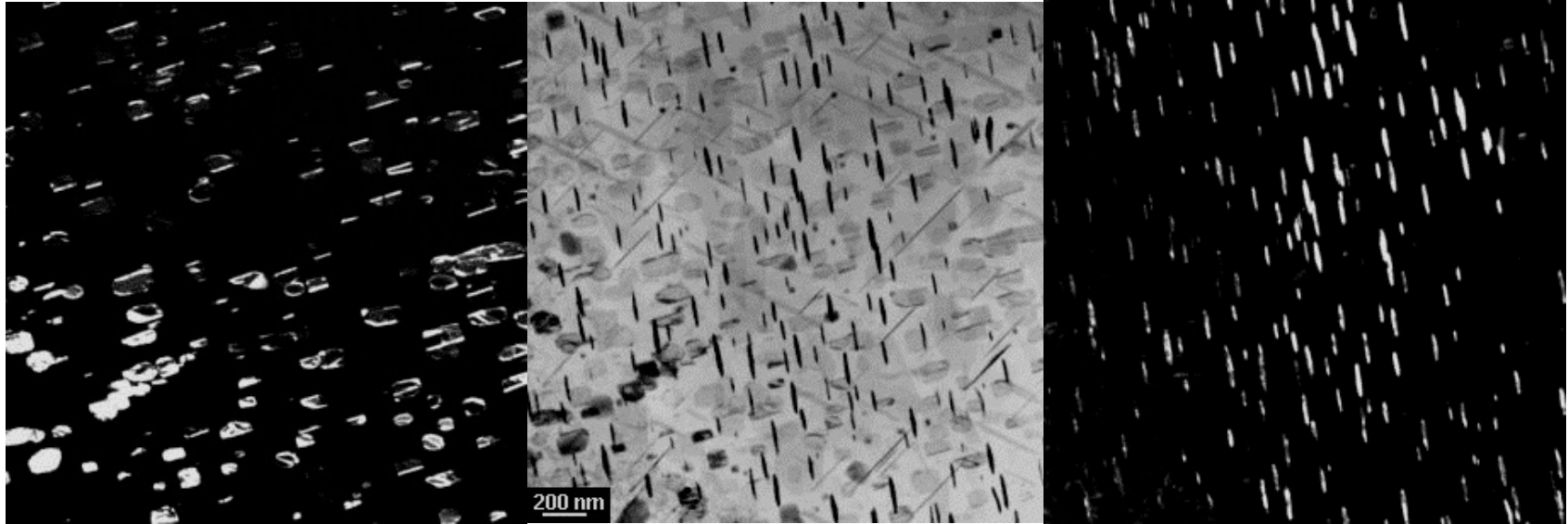


Dark-field image  $\mathbf{g} = (2\ 0\ 0)$



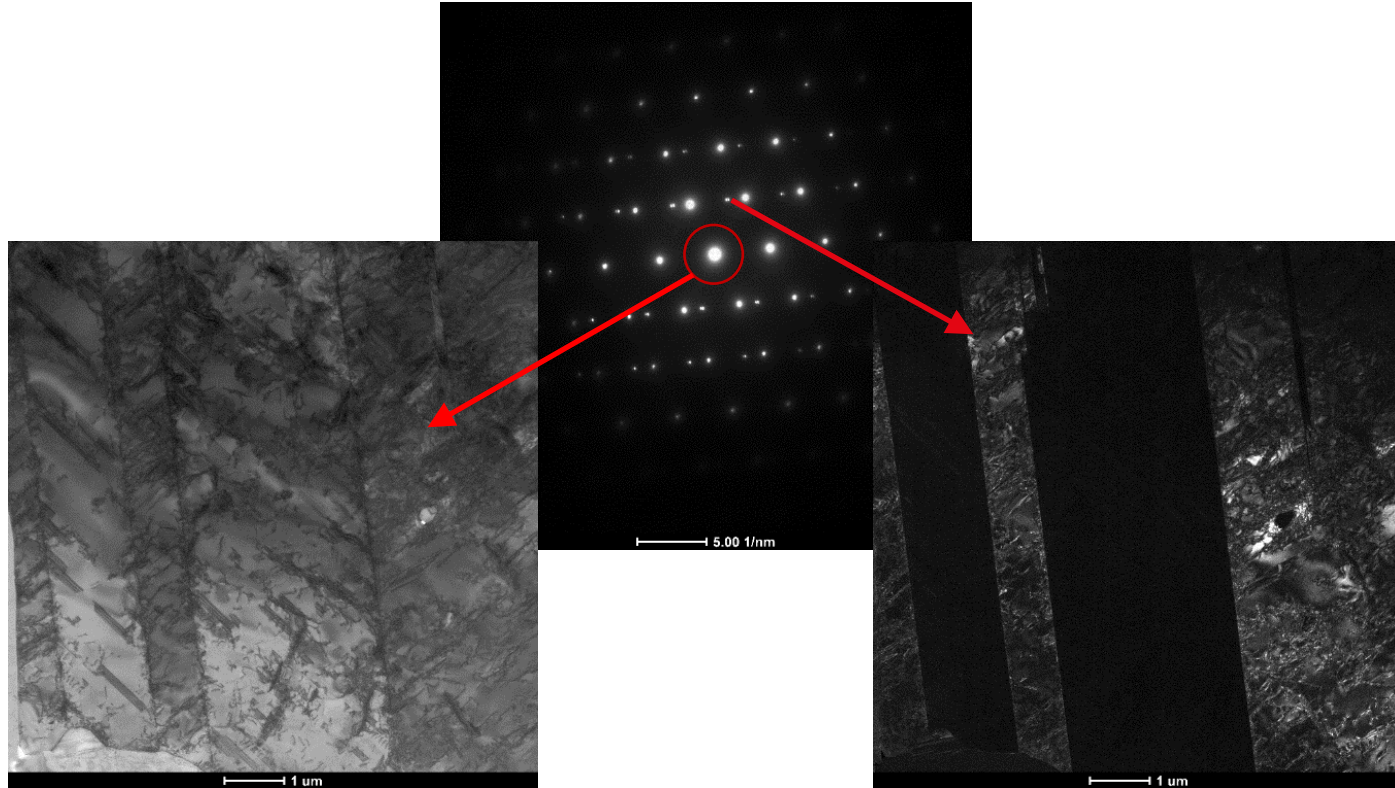
Dark-field image  $\mathbf{g} = (1\ 0\ 0)$

Example: Aluminum alloy containing precipitates with preferential growth direction

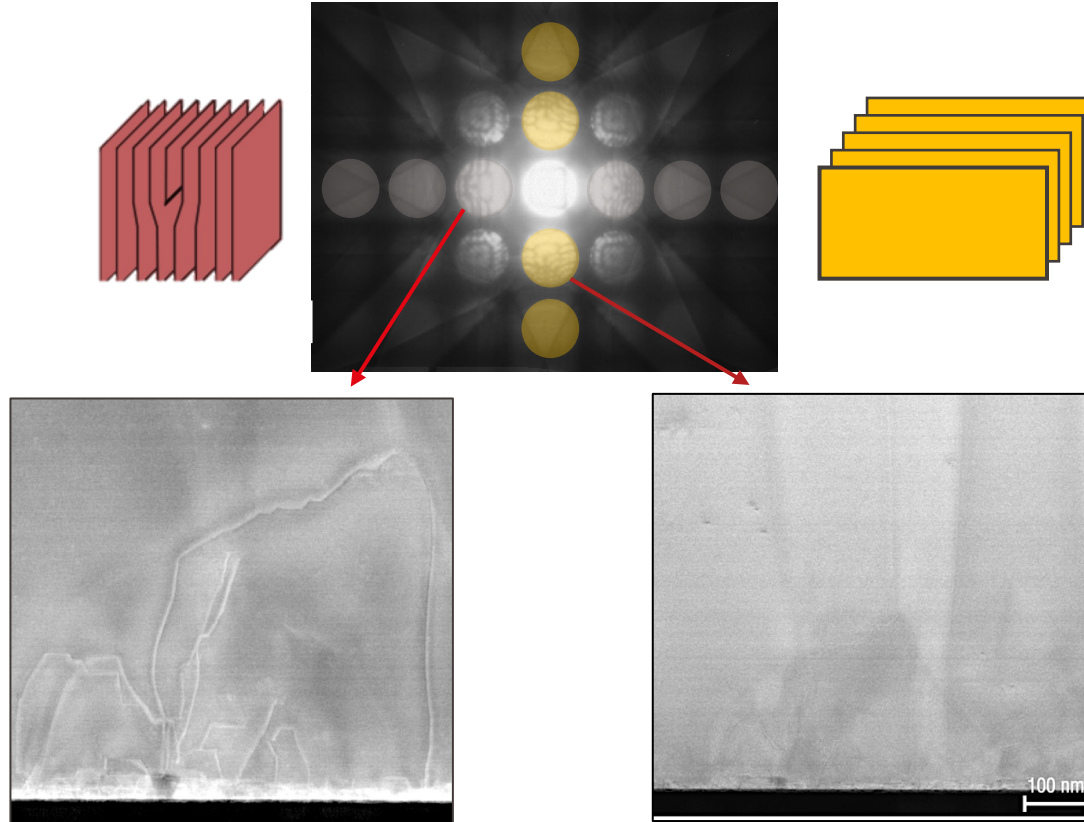


Orientation relationship between the matrix and precipitates can be determined

## Twinning in electron diffraction



Example: Dark-field images of dislocations in GaN thin film on sapphire



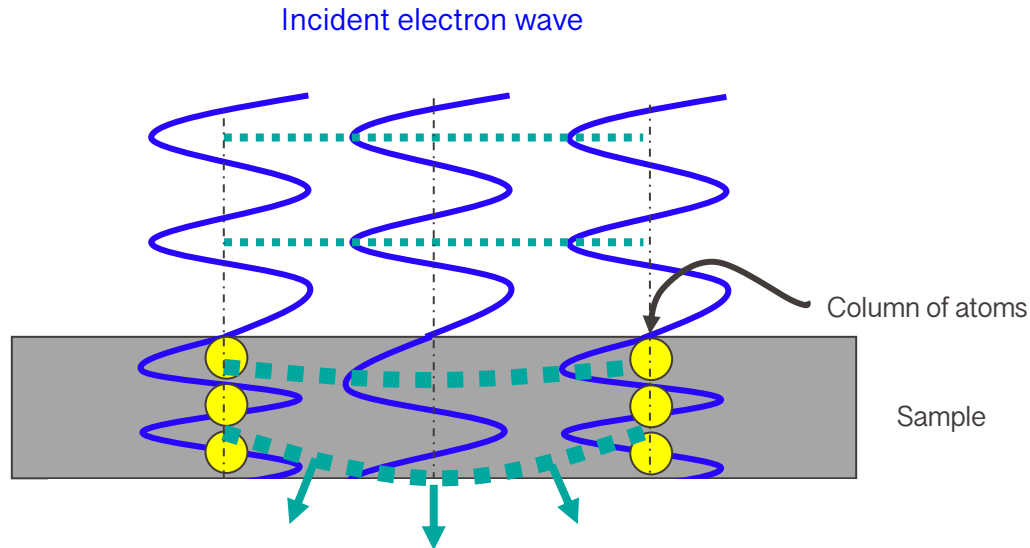
## ■ Image formation in TEM

- Image and diffraction modes
- Bright- and dark-field modes
- High-resolution TEM

## ■ Image contrast in TEM

- Mass-thickness contrast
- Diffraction contrast
- Phase contrast

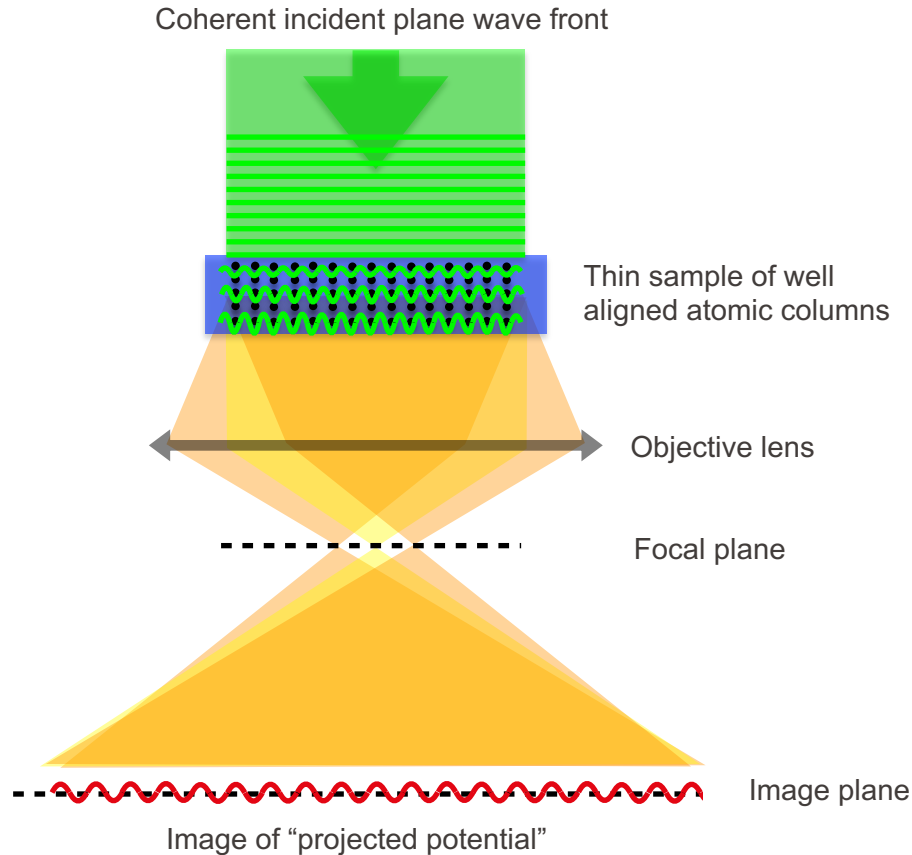
What happens when an electron wave passes through the sample?



Variations in the projected potential produce local relative phase shifts of the electron wave. The wave front therefore bends as wave travels through medium.

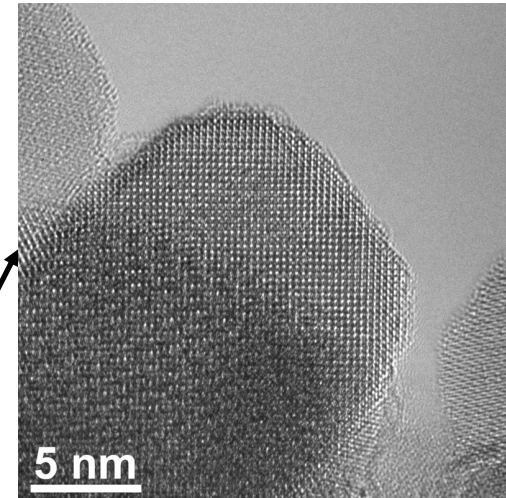
The direction of propagation of the electron may change!  $\Rightarrow$  Diffraction!





Due to changes in sample thickness and orientation, as well as lens imperfections, image interpretation is complex.

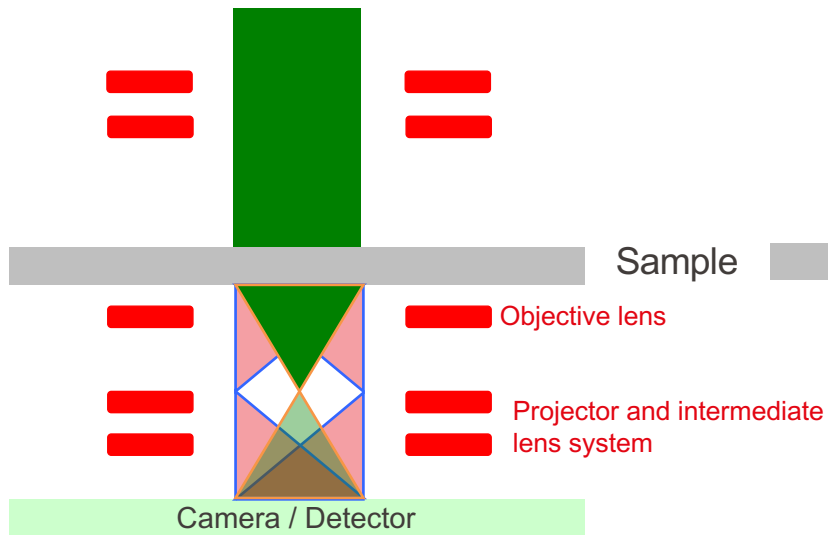
**Resist the temptation of interpreting the spots as atoms!**



Lattice fringes in iron oxide nanoparticles

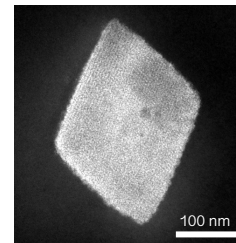
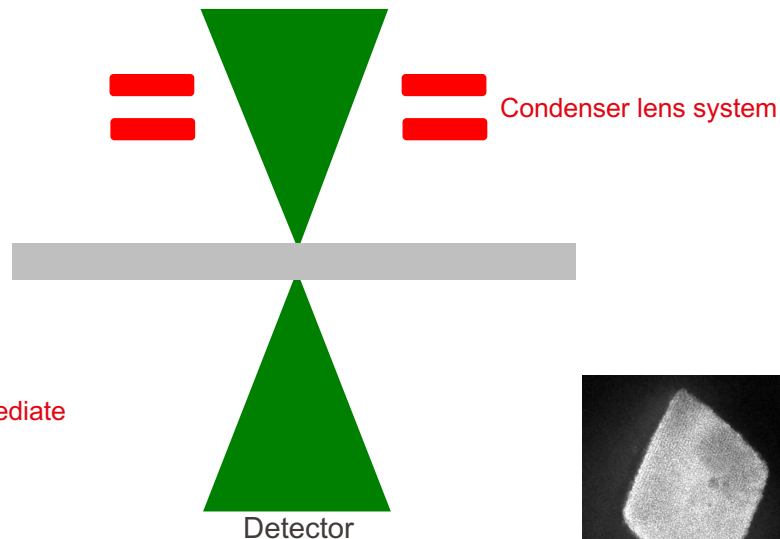
## Conventional TEM

Electron beam (60-300 keV)



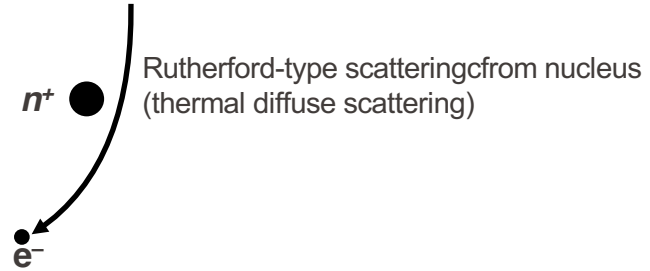
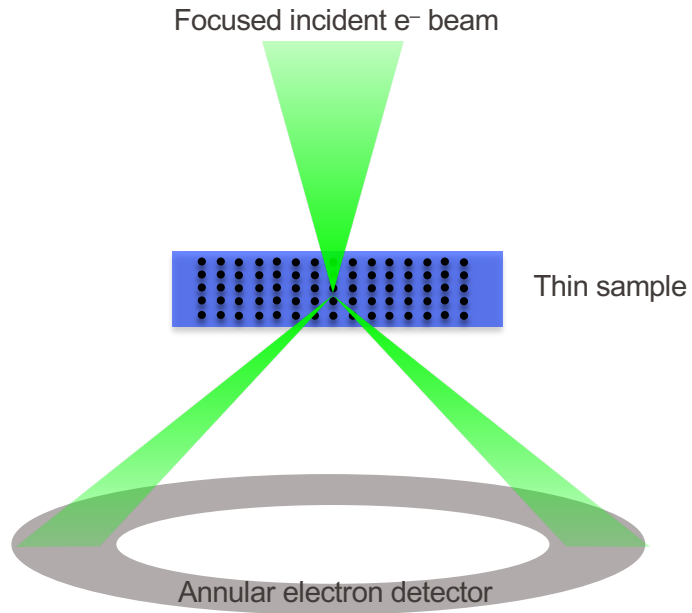
## Scanning mode (STEM)

Electron beam (30-300 keV)

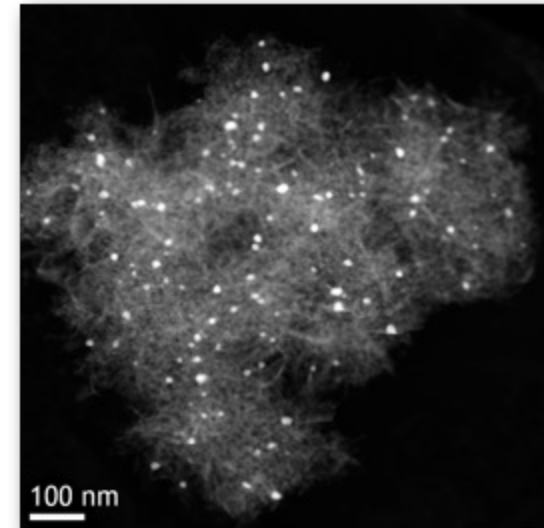


2D projection of a 3D object





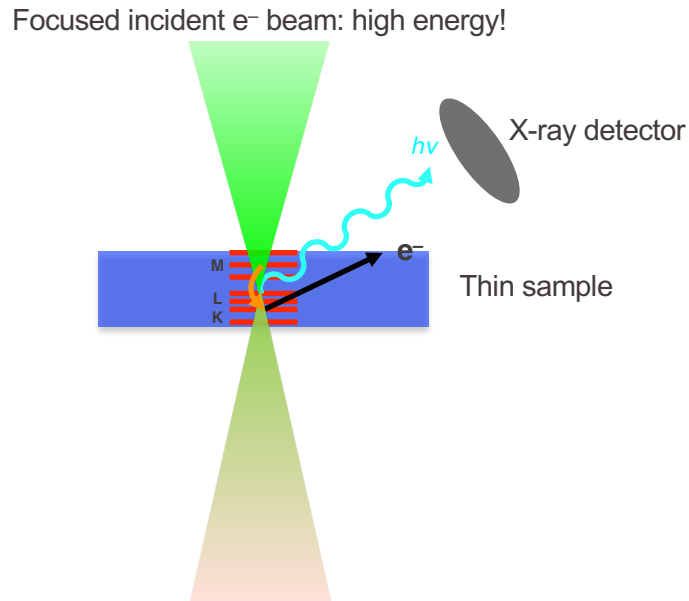
High-angle annular dark-field (HAADF) image



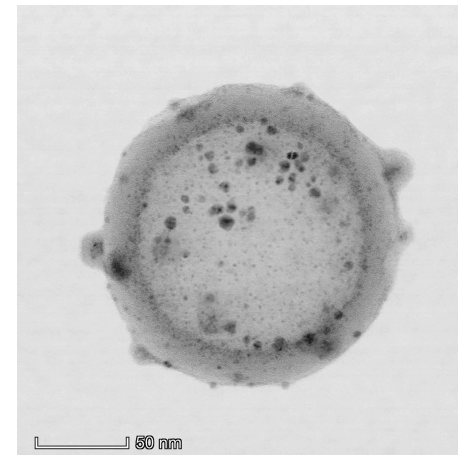
Pt catalyst particles on  $\text{Al}_2\text{O}_3$

- Incoherent Rutherford-type scattering deflects transmitted  $e^-$  to high angle of scattering
- Larger nucleus / thicker the specimen  $\rightarrow$  More scattering
- Map image intensity as function of probe position  $(x, y)$
- Image intensity:  $I(x, y) \propto t * Z^{1.6-2}$

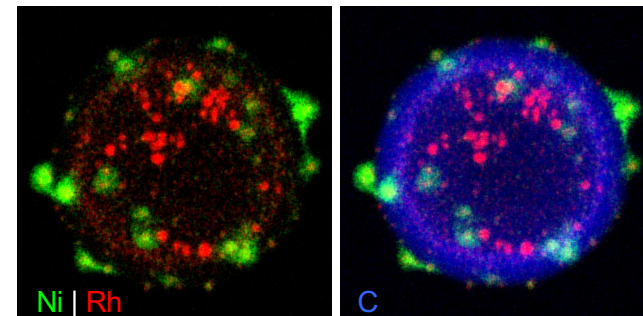
Mass/thickness contrast image



Bright-field STEM image



Ni-Rh catalytic nanoparticles in carbon shell



Map X-ray intensity as function of probe position (x,y)

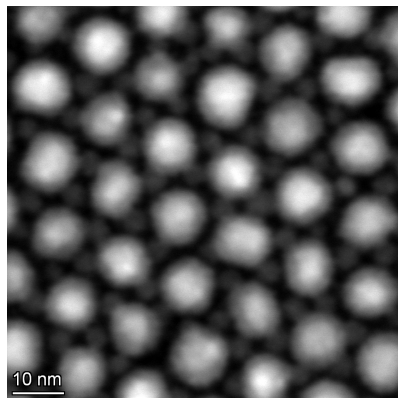
- High energy incident electrons (ballistic)  $\rightarrow$  Ejection of inner shell  $e^-$
- Upper shell  $e^-$  descends
- Transition energy emitted as X-ray;  
Characteristic of element |  $E_{X\text{-ray}} = E_{\text{Upper shell}} - E_{\text{Inner shell}}$

With fast mapping STEM-EDX has become a regular feedback tool for materials synthesis

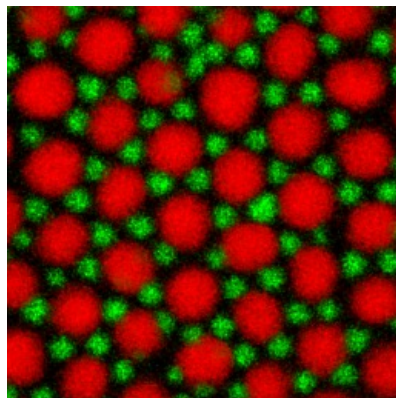
Sample characterized in a couple of minutes/hours

With aberration-corrected STEM, atomic resolution EDX became possible

Example : Assembly of  $\text{Fe}_3\text{O}_4$  and Cu particles

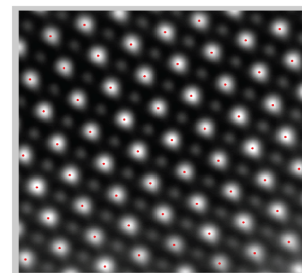


HAADF image

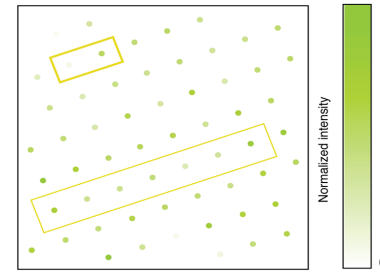


Map of Cu and Fe

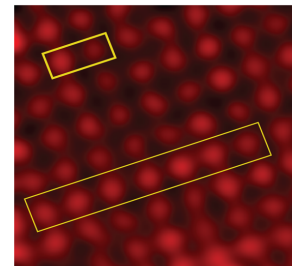
Example:  $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$



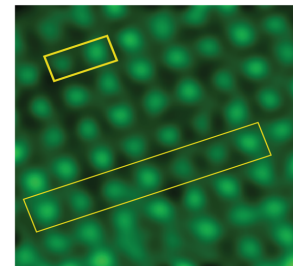
HAADF image



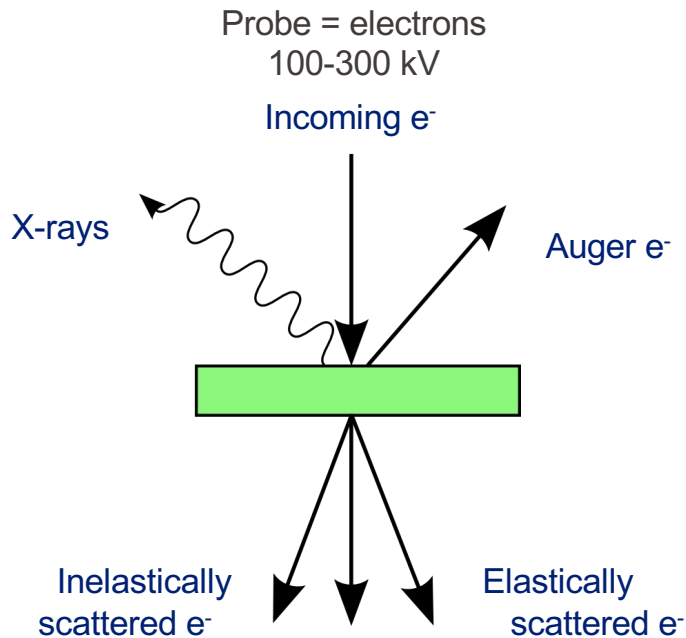
Intensity map

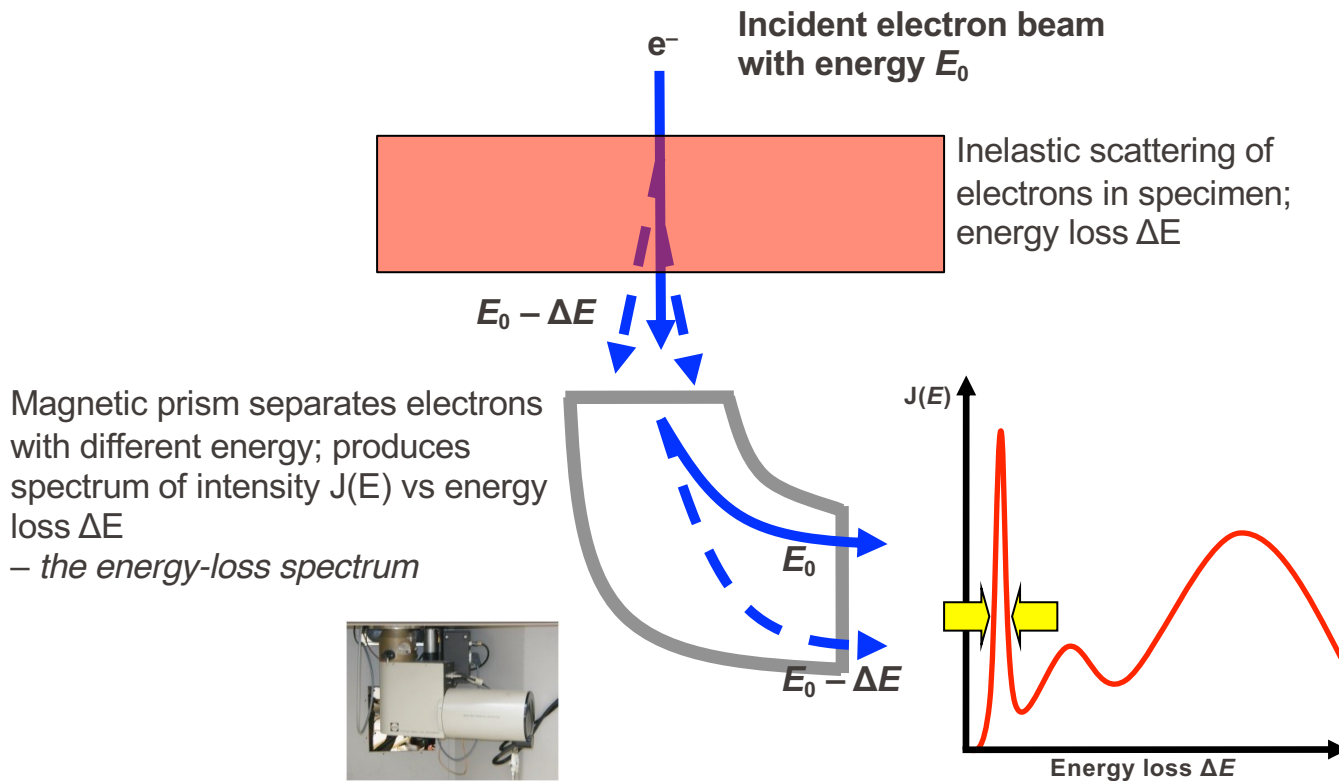


Map of Sr and Ba

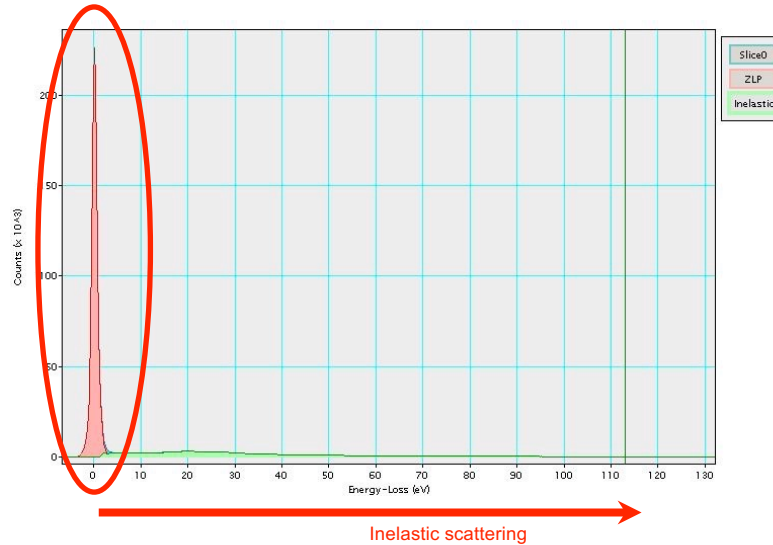


The TEM specific microanalysis technique!





e.g. Gatan Enfina

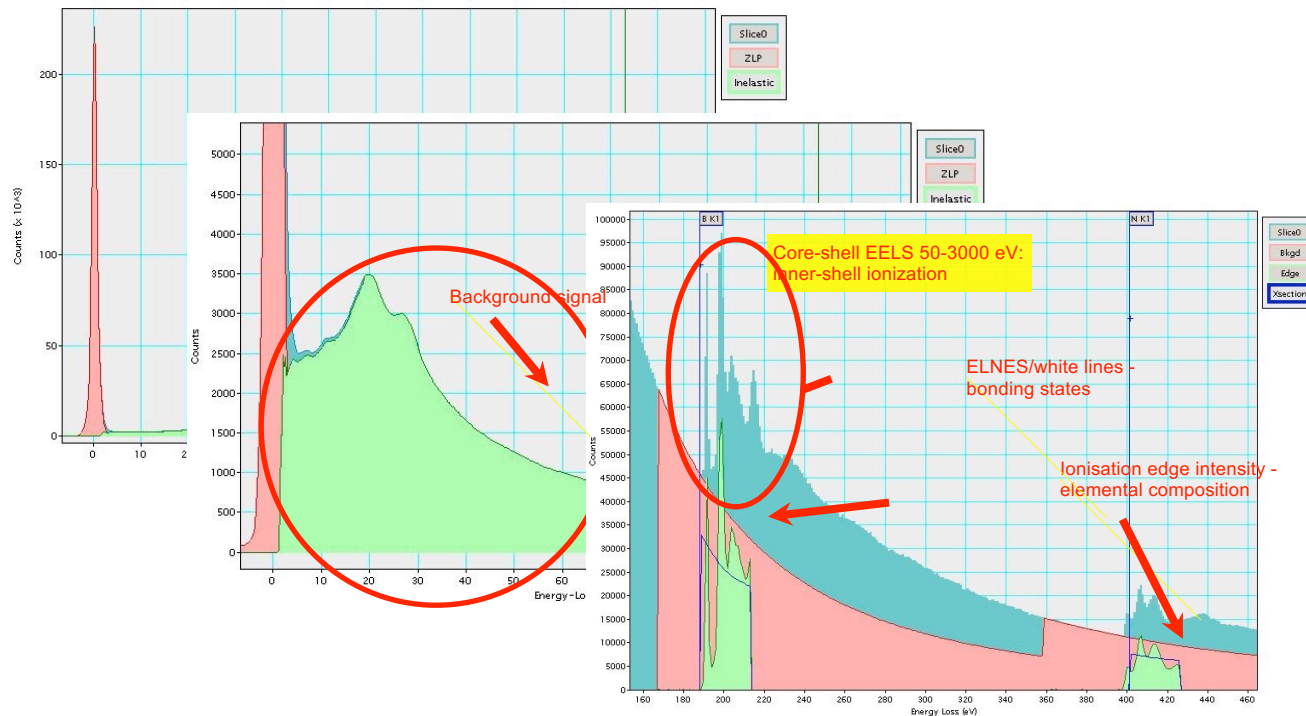


Zero-loss: Elastically-scattered  $e^-$   
Information about specimen thickness



## Interaction with outer electrons (conduction/valence)

Low-loss spectrum 0-50 eV: valence excitations -  
plasmons (bulk & surface),  
band gaps, optical properties



## Interaction with core electrons

Core-loss spectrum 50-3000 eV: inner shell ionization

ELNES/white lines: Bonding state

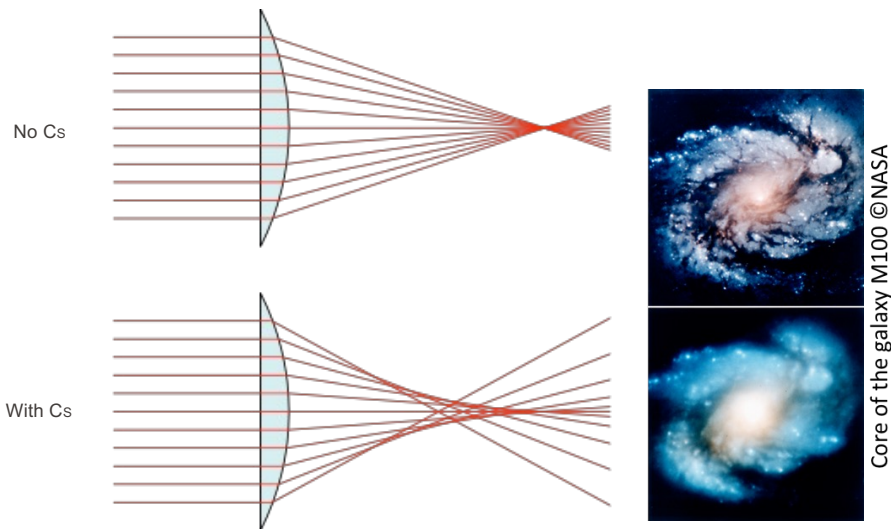
Ionisation edge intensity: elemental composition



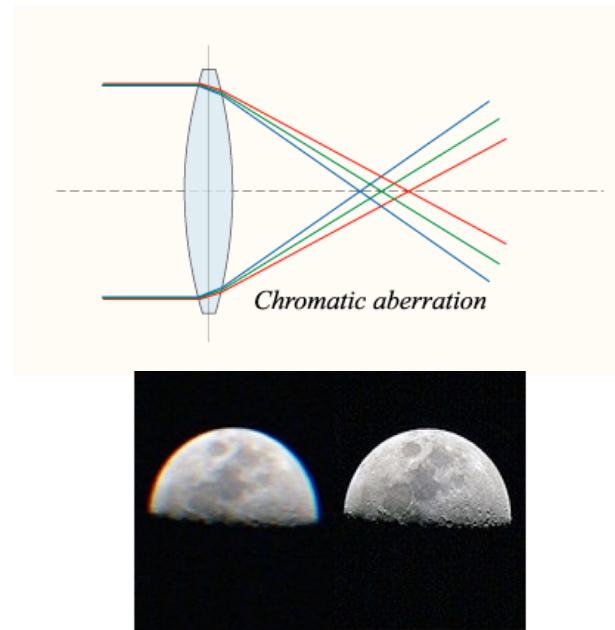
Electromagnetic lenses in TEM column are toroidal

Lenses inherently convergent

→ Spherical aberration ( $C_s$ ) and Chromatic aberration ( $C_c$ )



Parallel rays that pass through the central region of the lens focus farther away than the rays that pass through the edges of the lens. Results in multiple focal points and thus a blurred image.



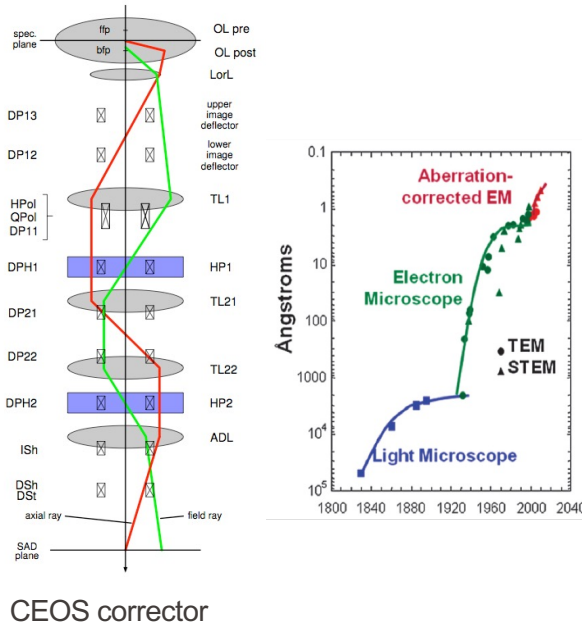
Lens cannot focus all energies (wavelengths) to the same convergence point.

*Resolution in TEM limited by aberrations, especially  $C_s$*

Combination of standard radially-symmetric convergent lenses with multipole divergent lenses (e.g. tetrapoles, hexapoles) to tune  $C_s$

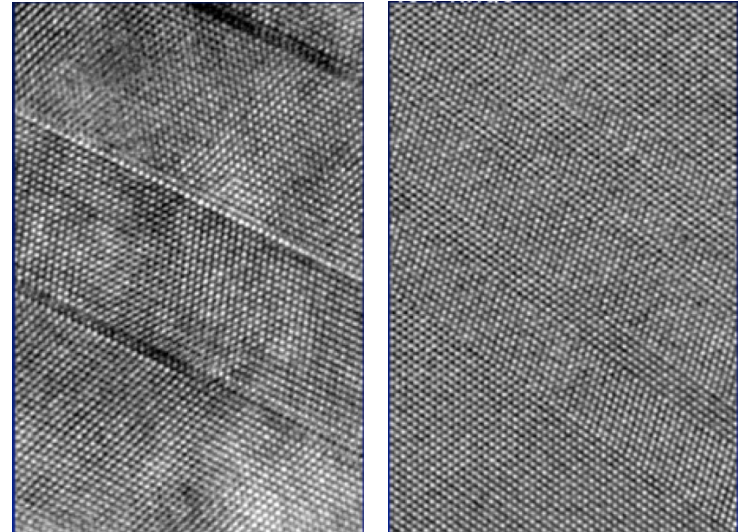
Like “glasses” for TEM (or the Hubble)

→ Resolution jumps to sub-Å!

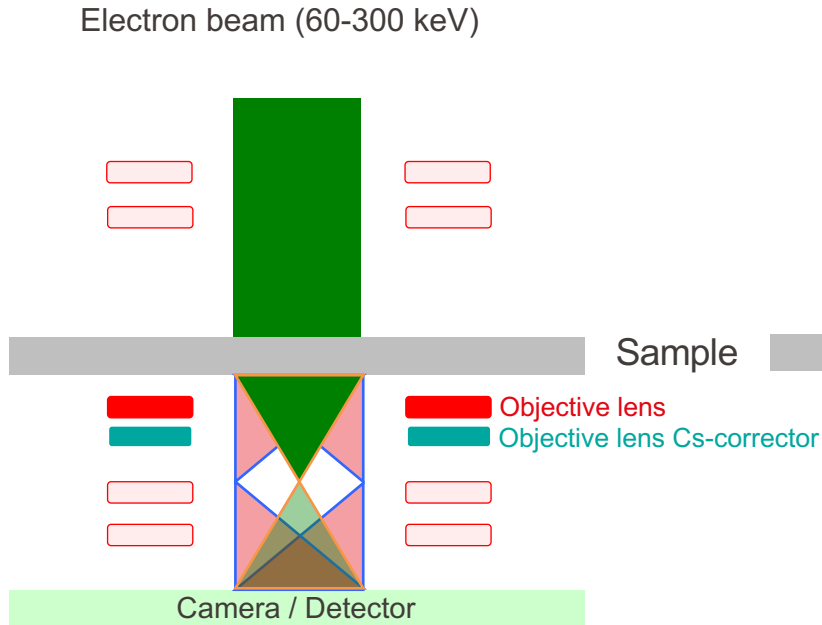
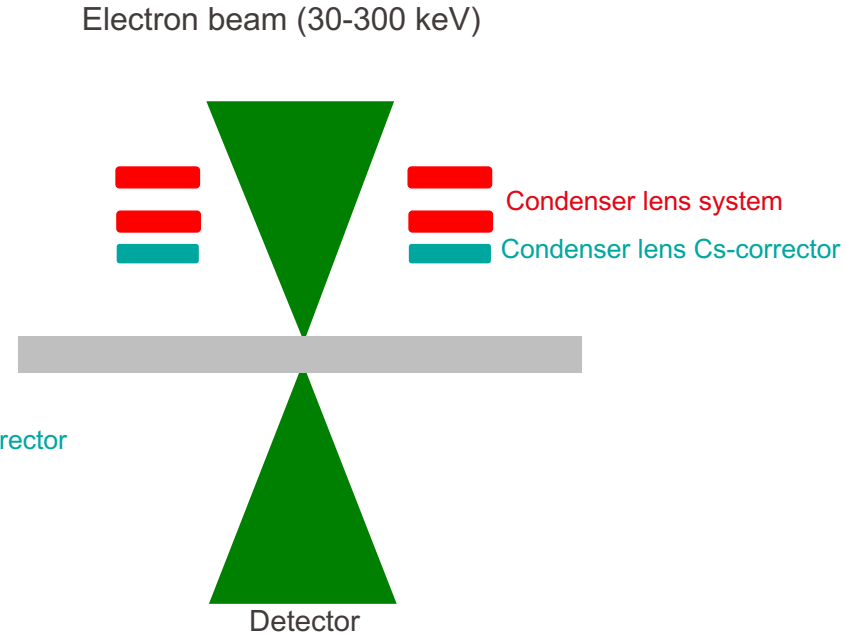


Example:  $\Sigma 3$  grain boundaries in Al

Uncorrected      Cs-corrected

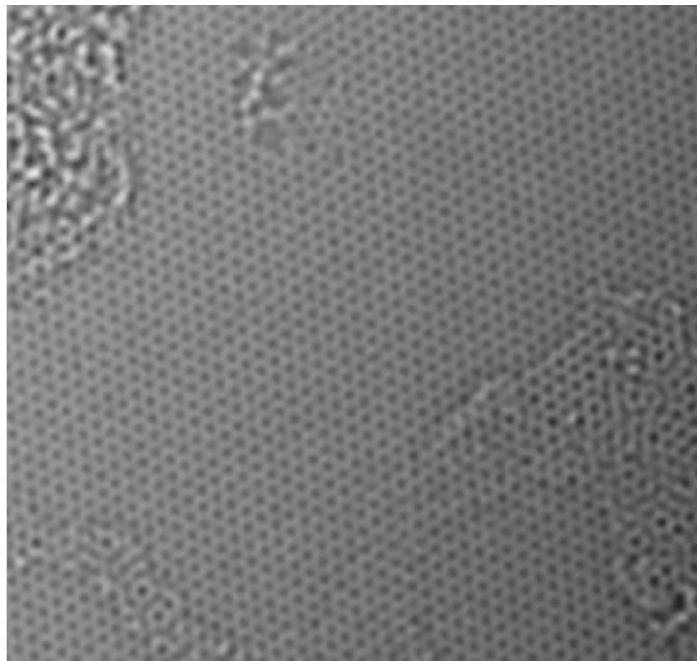


Images: Oikawa, JEOL

TEM (Image-corrected)STEM (Probe-corrected)

A double Cs-corrected S/TEM has both image and probe correctors

- Cs-correction and monochromatic illumination to reduce  $C_c$  allow sub-Å resolution even at lower kV where electron wavelength  $\lambda$  is greater
- Beam sensitive, low contrast materials can be imaged
- Here a monolayer graphene is imaged with 80 keV, monochromated  $e^-$



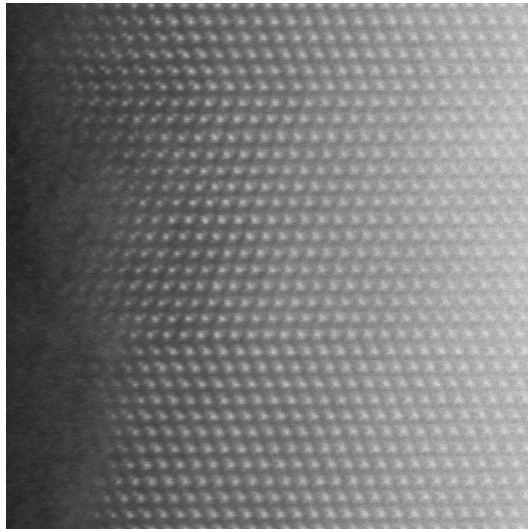
Example: (Al)GaAs nanowires imaged at 300 kV in STEM mode

## HR-STEM with sub-Å Cs-corrected probe:

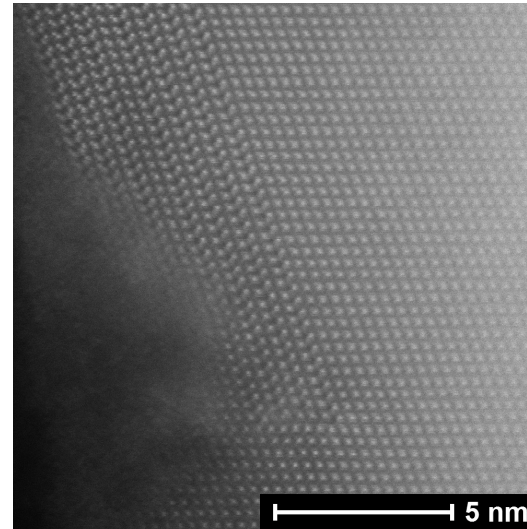
- Simple (quantitative) atomic column contrast

- Reduced sensitivity to small changes in sample orientation

- Image either in focus or out of focus (no contrast reversals with defocus, thickness)

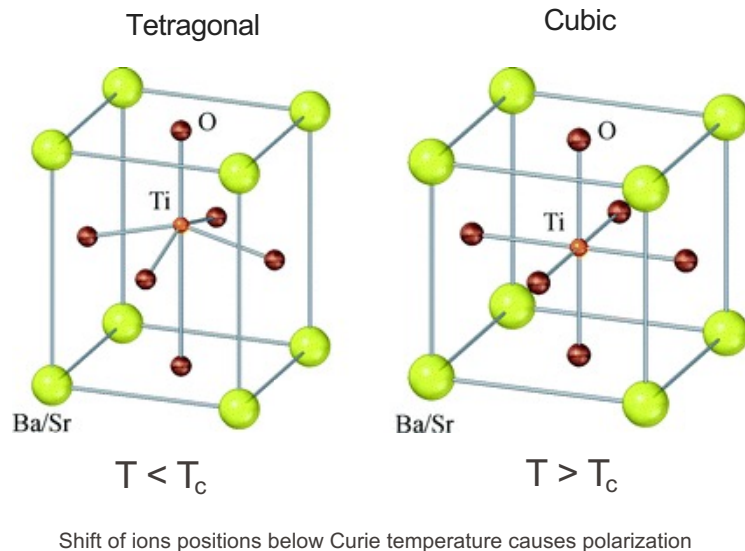


FCC twinning

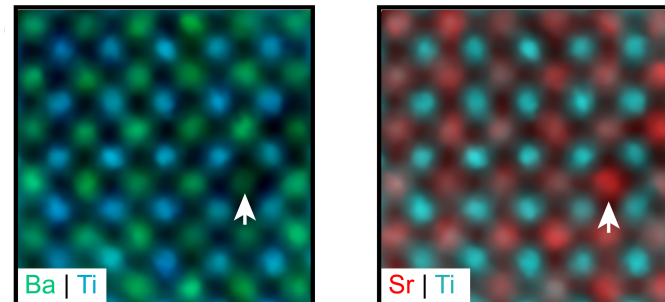


HCP inclusion and dislocation

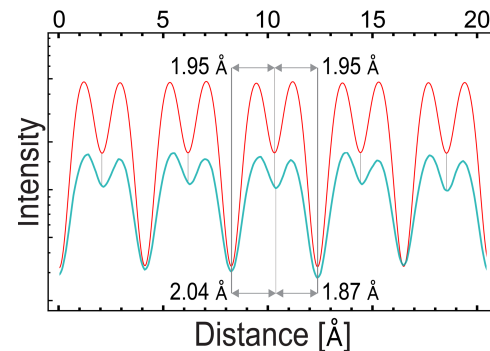
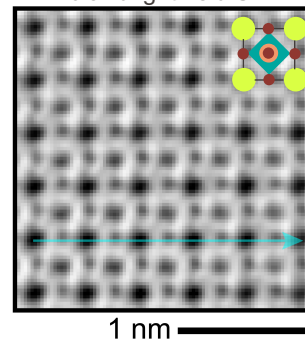
## Atomic scale symmetry and polar nanoclusters in the paraelectric phase of ferroelectric materials



STEM-EDX elemental maps of BSTO 60/40

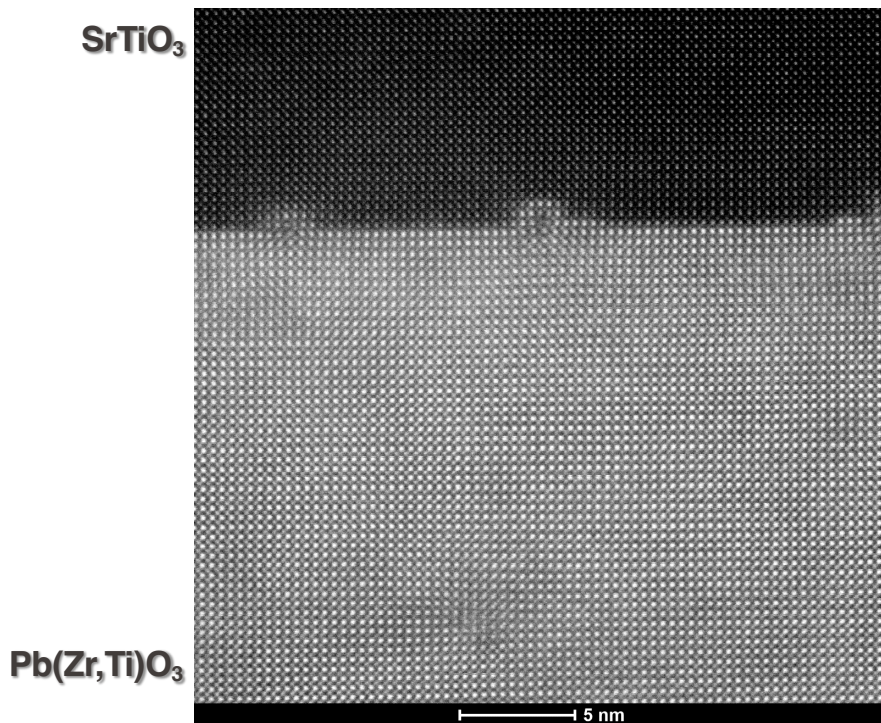


Annular bright-field STEM

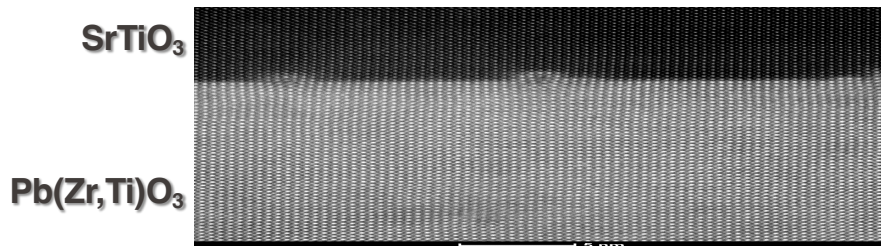




Cs-corrected atomic resolution HAADF-STEM of perovskite interface (300 kV)

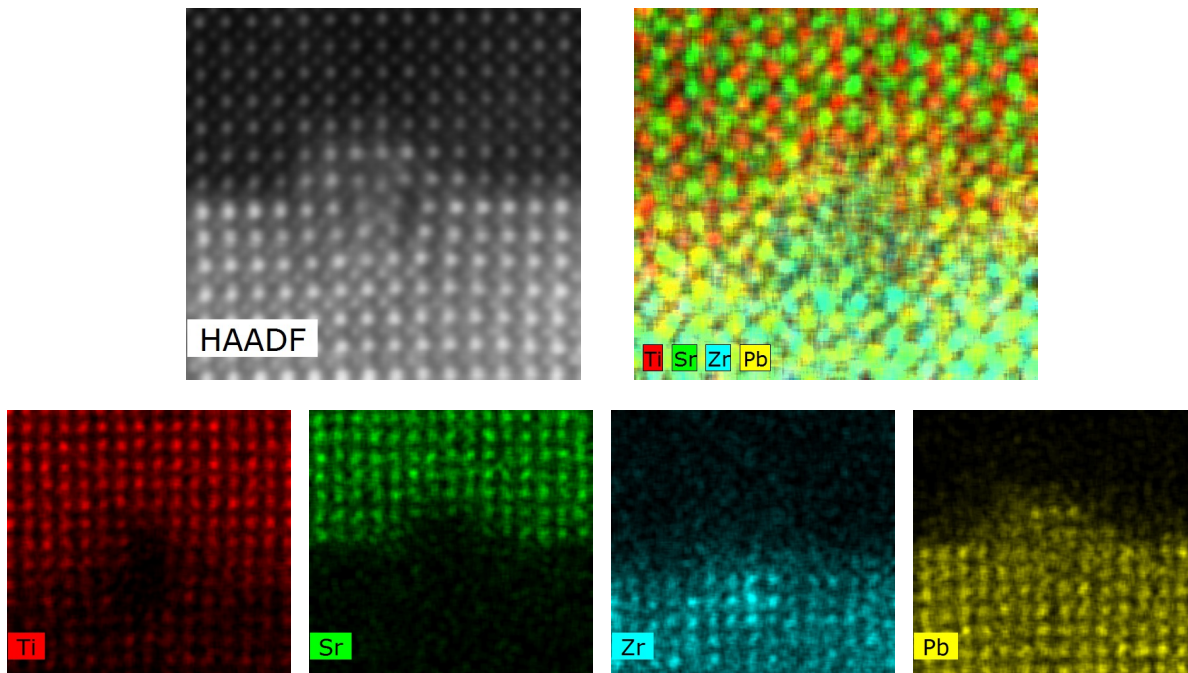


Cs-corrected atomic resolution HAADF-STEM of perovskite interface (300 kV)

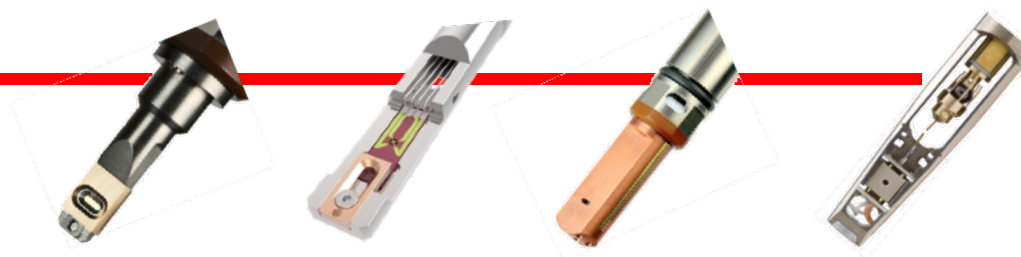
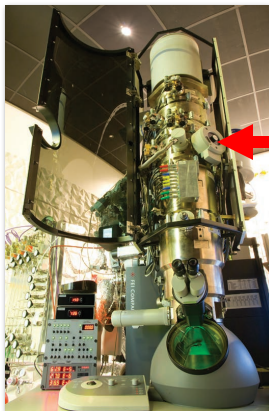




Atomic resolution STEM-EDX mapping reveals diffusion of Pb into strained region of misfit edge dislocation



Stimuli	Possible techniques	Information
<ul style="list-style-type: none"><li>• gas</li><li>• liquid</li><li>• temperature</li><li>• magnetic field</li><li>• current/voltage</li><li>• mechanical load</li><li>• light</li><li>• ...</li></ul>	<ul style="list-style-type: none"><li>• (S)TEM imaging</li><li>• diffraction</li><li>• electron energy-loss spectroscopy</li><li>• energy-filtered TEM</li><li>• energy-dispersive X-ray spectroscopy</li><li>• Lorentz microscopy</li><li>• holography</li><li>• ...</li></ul>	<ul style="list-style-type: none"><li>• microstructure</li><li>• crystallography</li><li>• chemistry</li><li>• diffusion/migration</li><li>• optical properties</li><li>• electric fields</li><li>• magnetic fields</li><li>• ...</li></ul>



Different dedicated holders

## **Liquid phase processes**

Hydration and other liquid phenomena  
Crystal growth from the liquid phase  
Corrosion

## **Phase transformations**

Solid state phase transformations  
    Crystallization and melting  
    Structural transformations  
    Solid state reactions  
Solid state transformations in nanostructured materials  
    Size-dependent transformations in embedded nanoparticles  
    Shape and phase transformations in free-standing nanoparticles  
    Sintering of nanoparticles

## **Elastic and plastic deformation**

Microscopic phenomena during plastic deformation  
    Deformation of polycrystalline materials  
    The effect of gas environment on deformation  
    Grain boundary motion  
    Deformation phenomena in single crystals  
    Deformation of multilayers  
Relaxation of epitaxially strained materials  
Mechanical properties of nanostructures, thin films and surfaces  
    In situ indentation and straining of thin films  
    Mechanical properties of nanostructures  
    Surfaces: Tribology and Nanomanipulation

## **Surface reactions and crystal growth**

Modification of surface structure  
Oxidation and other chemical reactions at surfaces  
Growth of nanostructures  
    Carbon nanotubes  
Thin film growth and defect formation  
    Epitaxial growth  
    Polycrystalline growth  
Crystal growth on patterned substrates

## **Domain wall motion and flux dynamics**

Magnetic domain switching  
Flux motion in superconductors  
Switching phenomena in ferroelectrics

## **Correlation of structural and electronic properties of materials**

Electrical measurements on TEM samples: samples as devices  
Electrical measurements on individual nanostructures

## **Beam induced processes**

Electron beam induced phenomena  
    Interaction with the vapour above the specimen  
    Formation of point defects  
    Beam induced transformations, surface reactions, growth  
    Radiation enhanced dislocation motion  
Hole drilling  
Ion implantation  
    High energy ion accelerators  
    FIB in the TEM

- A window into the behavior of materials under real processing conditions.
- A continuous view of a process, which may take the place of multiple post-mortem measurements.
  - It is easier to catch a transient phase or observe a nucleation event.
  - Specific and detailed kinetic information, such as the motion of individual dislocations under known stress, or growth rates of individual nanocrystals.
- This unique information comes at the cost of increased experimental complexity.
- Expensive: machine time, holders

TEM is now not one technique that can be easily summarised, but is split into many specialisms. In essence this is due to the many types of interaction of the electron beam with the atoms of a sample.

Modern TEM instruments are arguably the most versatile analytical tools. Many other possible uses (e.g. imaging of magnetic domains, optical plasmon mapping, in-situ studies) exist..

Aberration-correction and improved instrument stability give sub-Å resolution in TEM and STEM. With lower beam voltages lighter elements can be analysed without beam damage.

Faster, more sensitive spectrometers give unprecedented access to composition, chemistry and physics of materials.

Computer interfaces and software allow acquisition and processing of large datasets.

*With the latest instrumentation, the sample and specimen preparation are often the limiting factor!*

# Some useful literature

Transmission Electron Microscopy by D.B. Williams and C.B. Carter (Springer)

Large Angle Convergent Beam Electron Diffraction by J.P. Morniroli

Aberration-corrected imaging in transmission electron microscopy: an introduction by R. Erni

Scanning Transmission Electron Microscopy by S.J. Pennycook and P.D. Nellist (eds) (Springer)

Diffraction Physics by J.M. Cowley (North Holland/Elsevier)

Science of Microscopy by C.W. Hawkes and J.C.H. Spence (eds) (Springer)

Transmission Electron Microscopy: Physics of Image Formation and Microanalysis by L. Reimer